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# The Infrared Retina: Ushering in the Fourth Generation of IR Detectors

**Sanjay Krishna**

**Professor**

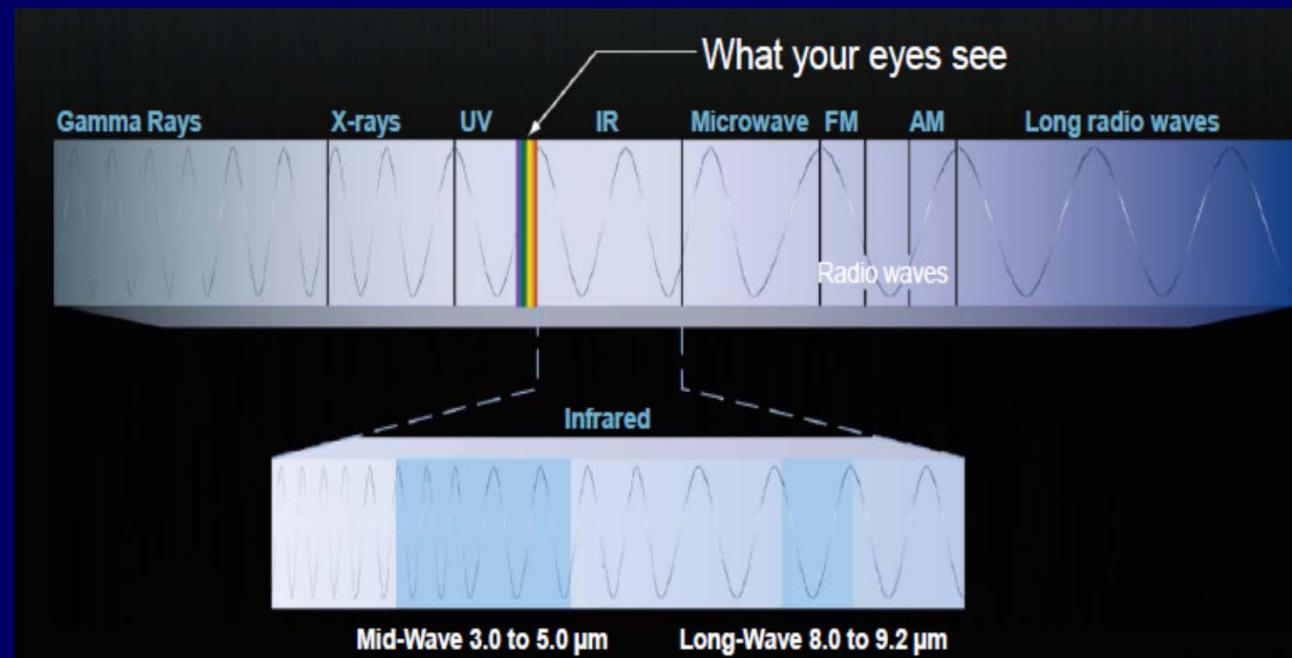
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Krishna INfrared Detector (KIND) Laboratory ([www.chtm.unm.edu/kind](http://www.chtm.unm.edu/kind))

# Outline

- ***Background and Motivation***
- ***Type II Strain Layer Superlattices***
- ***Quantum Dots in a Well Detectors***
- ***4<sup>th</sup> Gen Imagers: The Infrared Retina***





# Krishna Infrared Nanostructure Detector (KIND) Laboratory



## Collaborators

- Brueck, Hayat, Ha (UNM)
- Javey Group (Berkeley)
- Noh/Lee (KRISS)
- Cardimona (AFRL/VSSS)
- Gunapala Group (JPL)
- Painter Group (Caltech)
- QmagiQ LLC
- Raytheon Vision Systems
- Lin Group (RPI)
- Vandervelde (Tufts)
- SK Infrared LLC
- CINT /SNL (Brenner/Peters)

## Past Group Members

- POSTDOCs: Dr. A. Amout (Emcore), Dr. P. Dowd (ASU), Dr. J. Brown (Micron), Dr. J.B. Rodriguez (Montpellier), Dr. T. Vandervelde, (Tufts); Dr. M. Naydenov Lightspin
- PhDs: Dr. Winckel, Uni. Graz; Dr. Zhu, Law Firm; Dr. Plis, UNM; Dr. Attaluri, Lehigh Univ.; Dr. Newmann, Emcore; Dr. Andrews, NRL; Dr. Wilcox, NRL, Dr. Khoshakhlagh (JPL), Dr. Hasul Kim (UCB), Dr. Rajeev Shenoi (RPI), Dr. David Ramirez (UNM), Dr. Jiayi Shao (Purdue); Dr. Ajit Barve (UCSB)
- M.S.: N. W. Bernstein, LANL, J. Shelton, SNL, G. Bishop, SNL, E. Varley, D. Jepson, AFRL; M. Lenz, SNL, K. Posani, Qualcomm, C. Wilcox, NRL, S. Annamalai, Triquint, M. Serna, Oxford; S. Raghavan

## Senior Researchers

- Dr. Tom Rotter
- Dr. Elena Plis
- Dr. Y.D. Sharma
- Dr. Z.B. Tian
- Dr. J.O. Kim
- Dr. D. A. Ramirez

## Graduate Students

- Stephen Myers
- John Montoya
- Eric Jang
- Freddie Santiago
- Maya Kutty
- Nutan Gautam
- Brianna Klein
- Ted Schuler Sandy
- Glauco Fiorante
- Vince Cowan
- Marziyeh Zamiri
- Ali Shirazi
- Nathan Henry (UG)

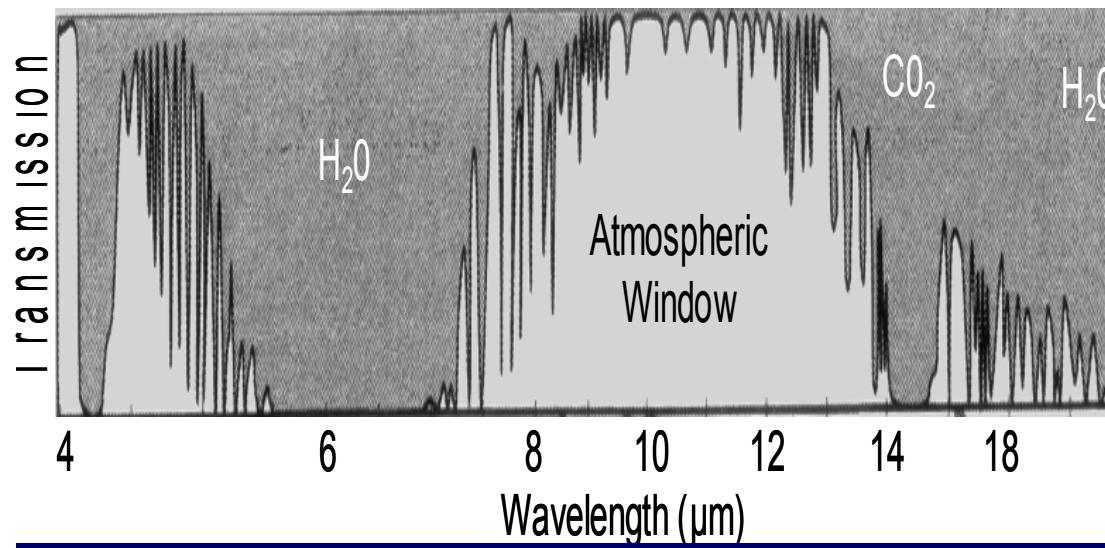
## Funding Agencies

AFOSR, AFRL, NSF, IC,  
DIA, DARPA, KRISS-GRI

# Infrared Imaging: Background and Applications

## Applications

- Defense and Security
- Medical Diagnostics
- Surveillance
- Astronomy
- Home inspections
- Fire fighting
- Entertainment





# The Infrared Imaging Market

- Low Volume, High Performance, High Cost (\$300K-500K)
  - Requirements: High quantum efficiency, extremely low dark current, no cost or operating temperature limit
  - Applications: low background applications, such as Astronomy
  - MWIR-InSb, LWIR-MCT, VLWIR- Si:IBC
  - **Type II SLS**
- Large Volume, Uncooled Operation, Low Cost (\$5K-20K)
  - Low cost, slower speeds, room temperature operation, no spectral information
  - Bolometers
- Intermediate Volume, Performance and Cost (\$70K-100K)
  - Desired Features: Low dark current, moderate quantum efficiency, high operating temperature, large format, multicolor, intermediate cost
  - Current players: MWIR-InSb, LWIR-QWIP
  - **QD Detectors**

# Historical Perspective

## First Gen Systems

- Single Pixel
- Linear Arrays

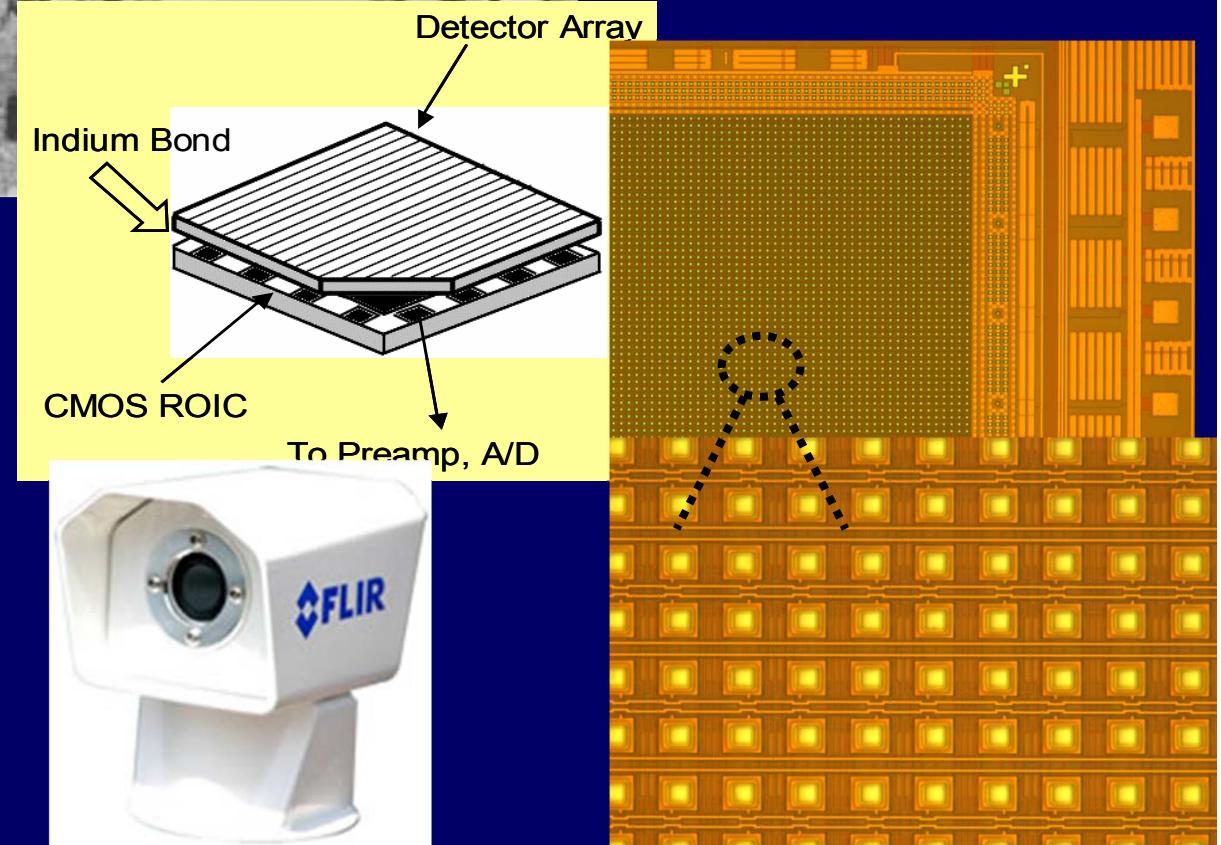


## Second Gen Systems

- 2D Staring Arrays
- Mostly Single Color

## Third Generation Systems

- Higher Operating Temperature (HOT)
- Multicolor Capability
- Large Format Arrays



# Skin Cancer in the US

## Skin Cancer Facts

- Most common type of cancer in US
- More cases of skin cancer than those of breast cancer, prostate cancer, lung cancer and colon cancer combined.
- One in every five Americans develops skin cancer in their lifetime.
- Melanoma is the deadliest form of cancer and is responsible for 75% of Skin Cancer related deaths (~70,000 deaths in 2009)

## Current Technology

### Subjective Visual Test



OR

### Invasive Biopsy



**Early diagnosis is key in preventing the occurrence of skin cancer**

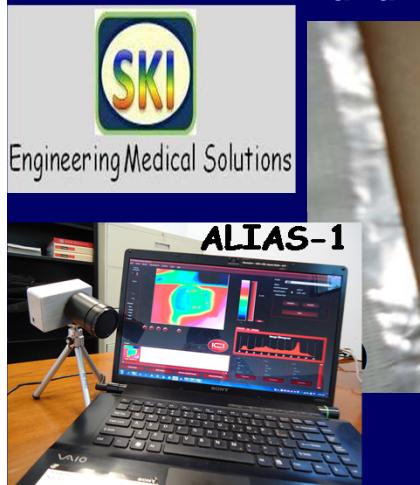
\*Rates are per 100,000 and are age-adjusted to the 2000 U.S. standard population.

†Source: U.S. Cancer Statistics Working Group. [United States Cancer Statistics: 1999–2006 Incidence and Mortality Web-based Report](http://www.cancerstatistics.gov).

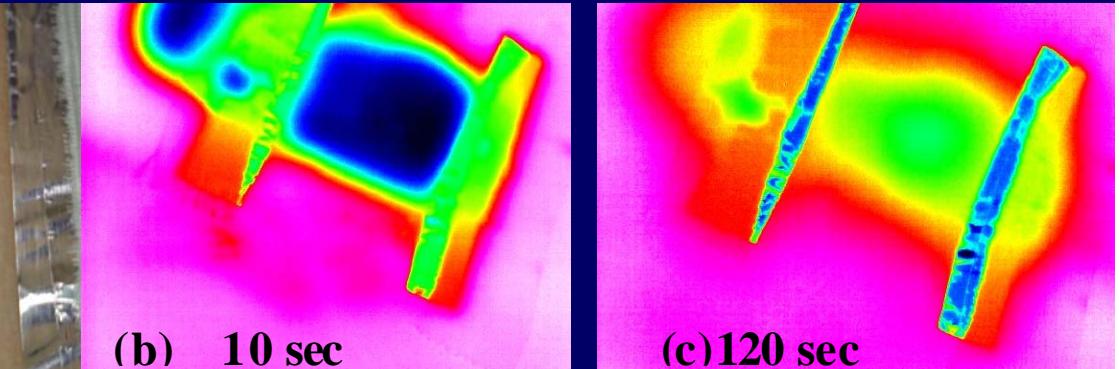


# Early Detection of Skin Cancer with IR Imaging

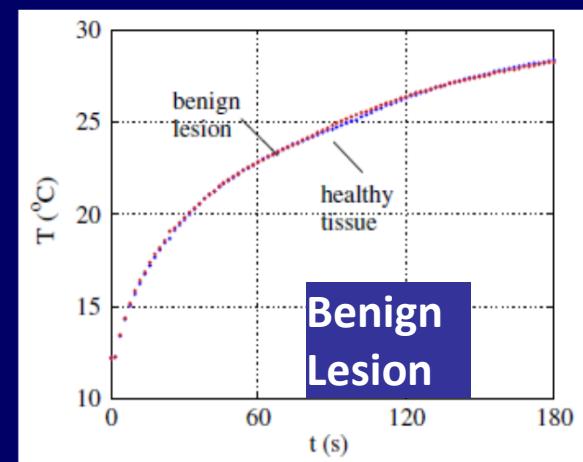
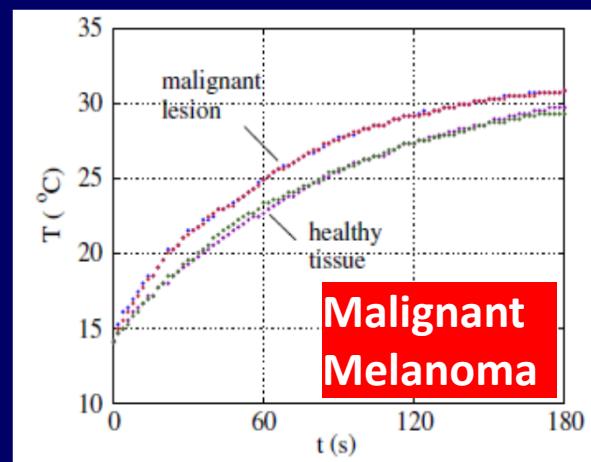
(a)Visible image of a benign dysplastic nevi and infrared images at (b) 10 seconds and (c) 120 seconds after cooling using ALIAS-1 developed by SK Infrared LLC



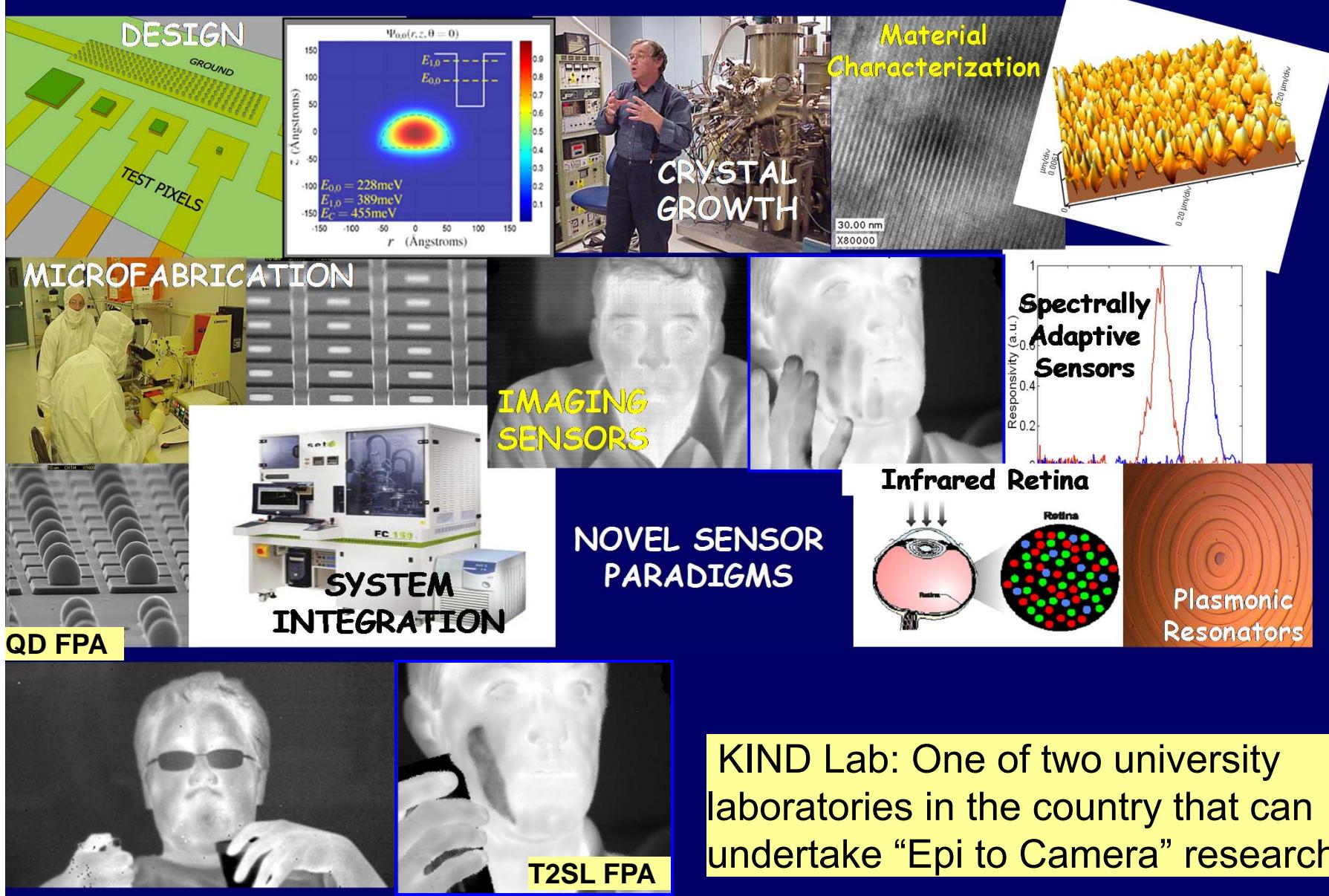
*Advanced Longwave  
infrared Imaging  
Analysis System  
(ALIAS)*

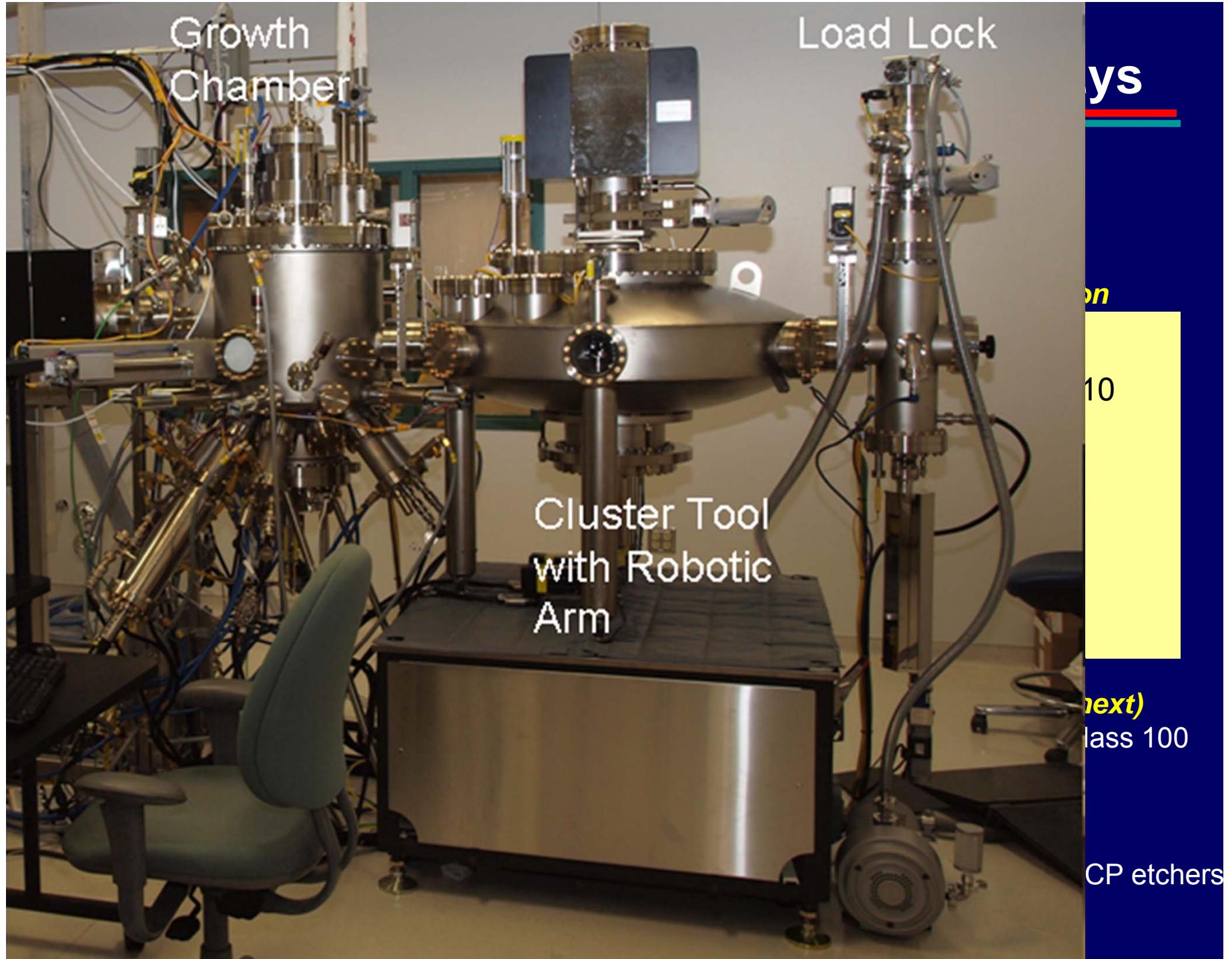


No significant difference was observed in the response of the nevi and the surrounding skin, indicating a benign lesion



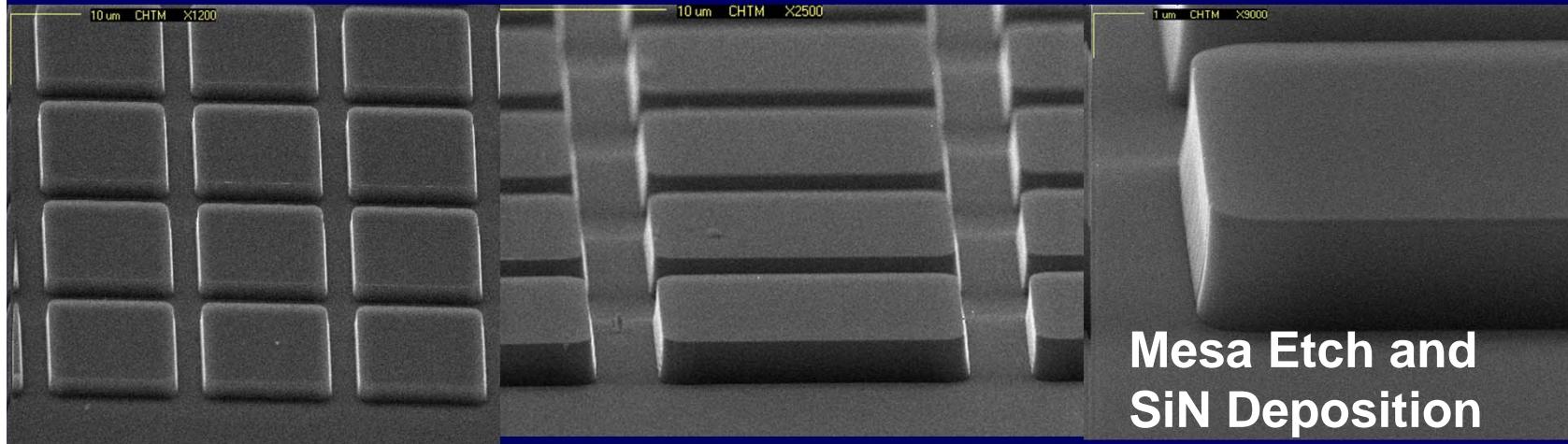
# Epi to Camera Research







# Processing: Material to FPA

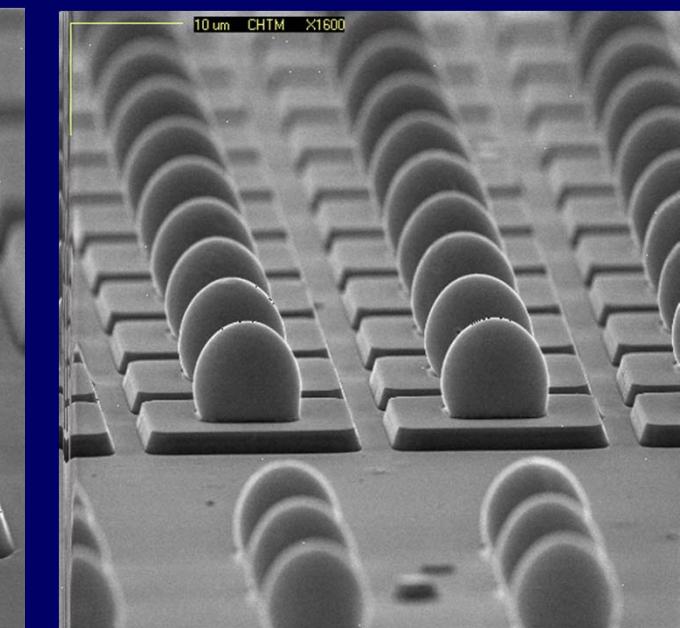
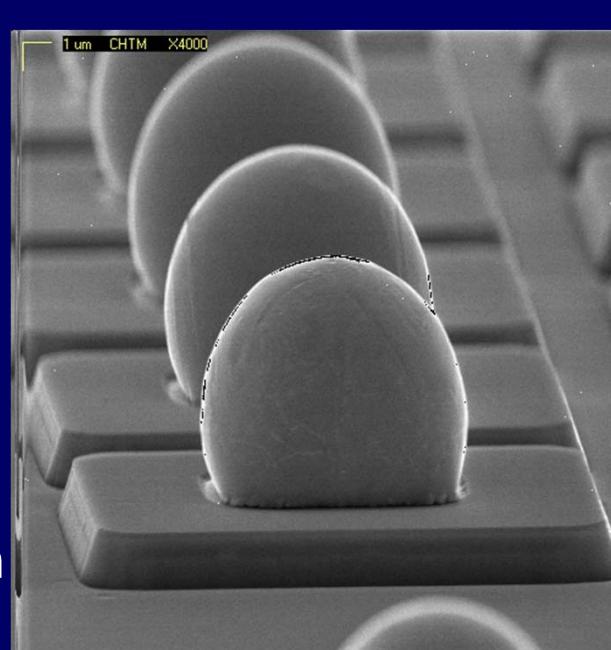
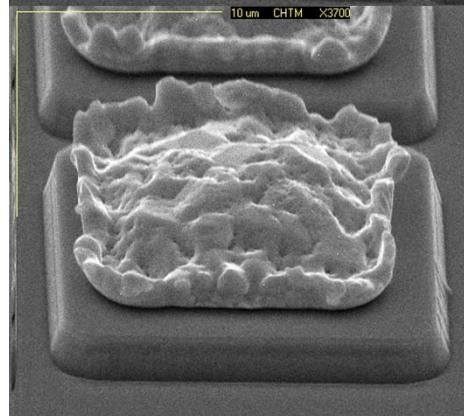
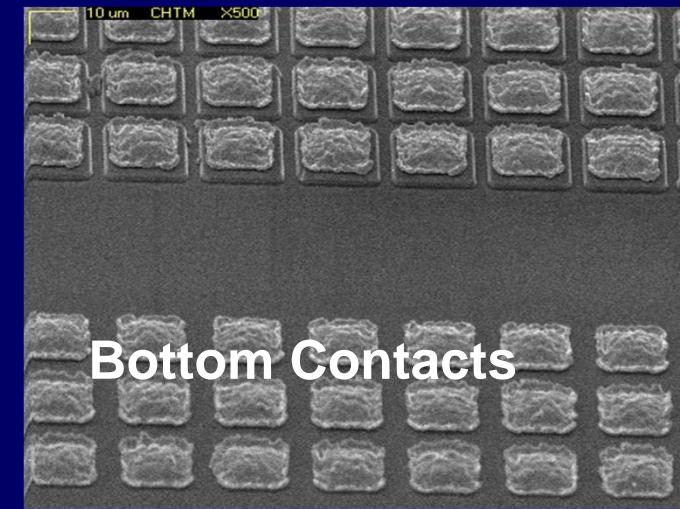
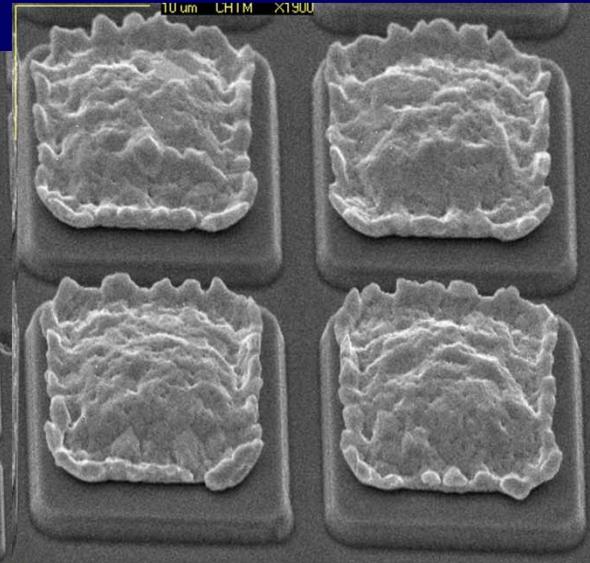
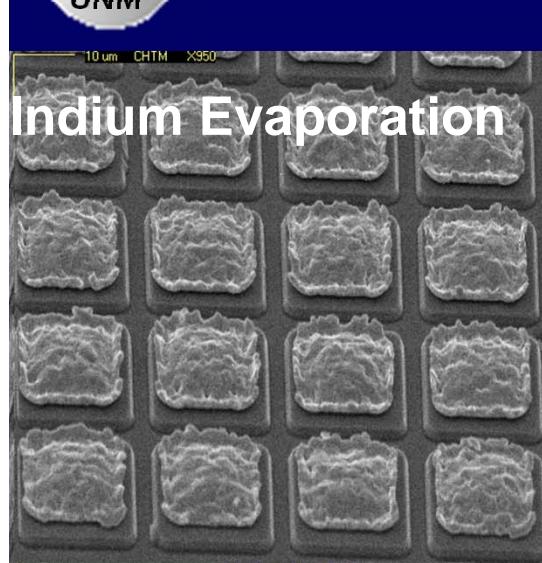


Mesa Etch and  
SiN Deposition



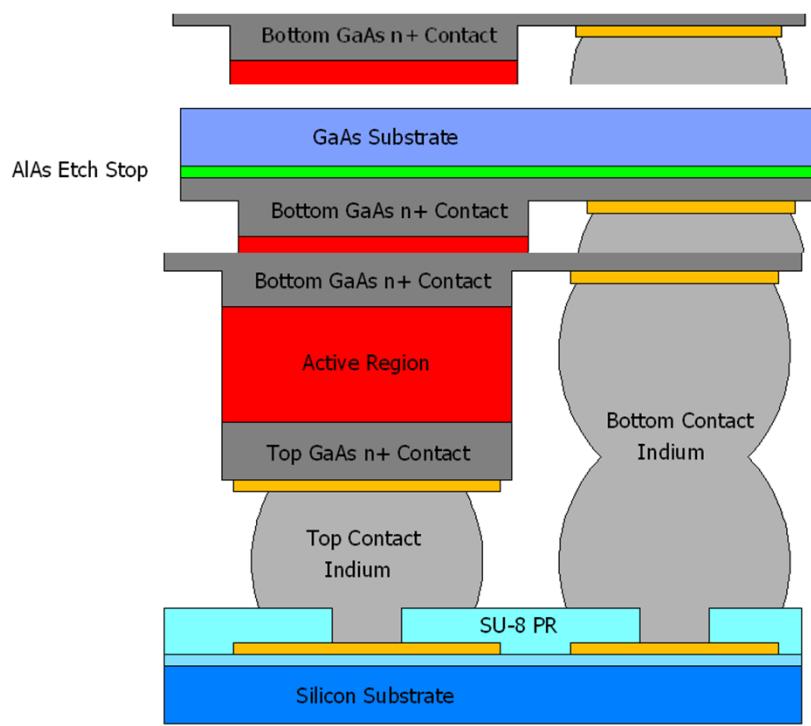
Contact Metal Deposition

# Processing: Material to FPA



After Indium  
Reflow

# Processing: Material to FPA



## ***STEP 4: Indium Bump Metallization/Dicing***

- Establish a process for indium bump metallization and dicing of wafers

## ***STEP 5: Hybridization to Fanout/ROIC***

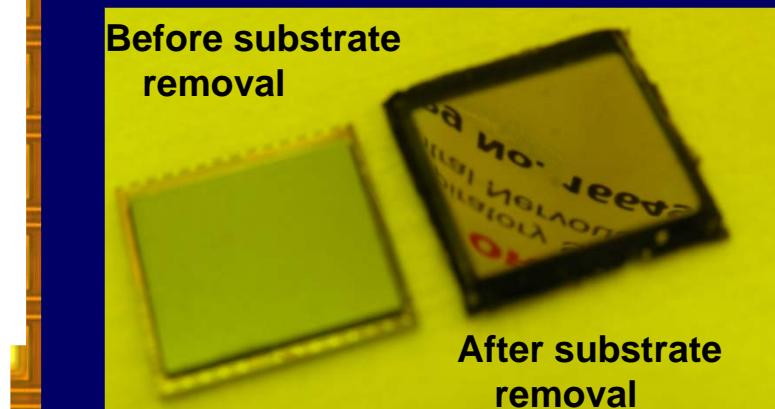
- Test structures are hybridized to Fanout
- After initial characterization, the actual ROICs are hybridized

## ***STEP 6: Substrate Removal***

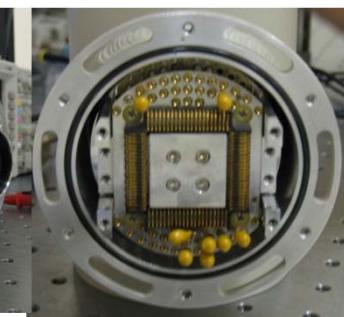
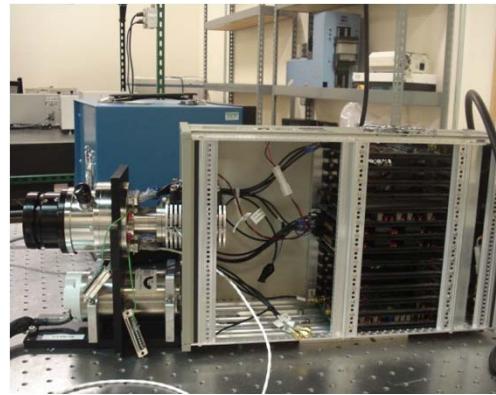
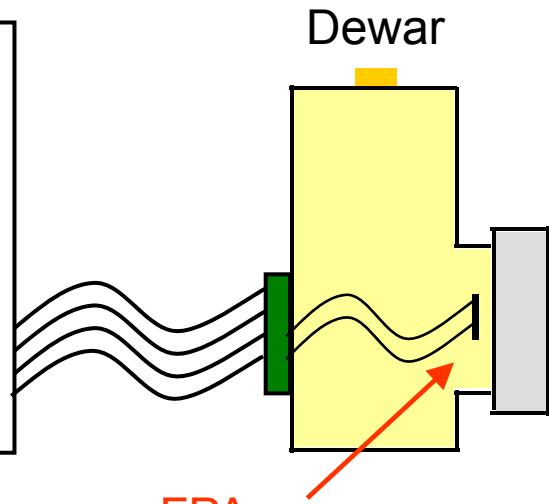
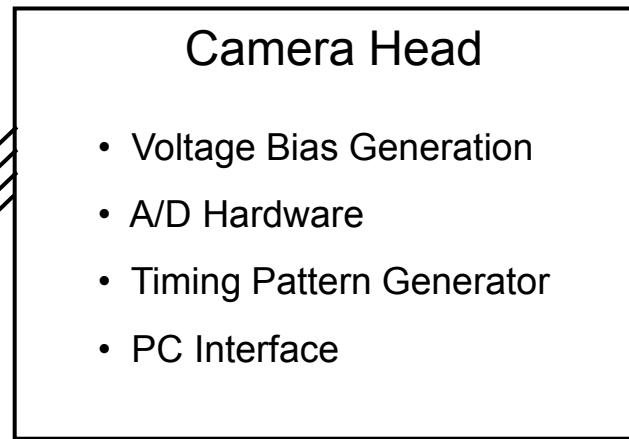
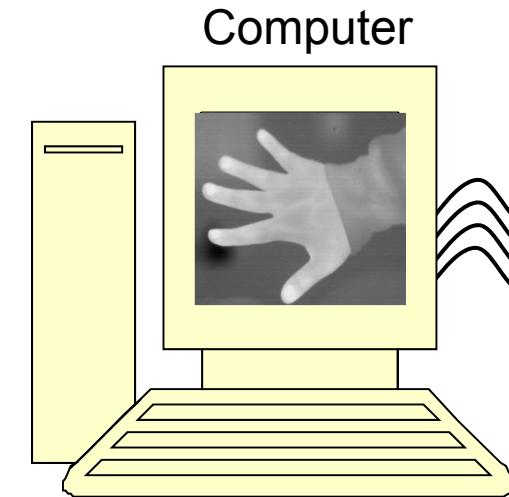
- Substrate will be removed by a combination of chemical and mechanical polishing

## ***STEP 7: Characterization and Evaluation***

- Performance of devices will be evaluated
- FPA characterization will be undertaken



# Mid-infrared Imaging Characterization and Applications (MICA) Lab



- **Commercially available SE-IR CamIRa™ demonstration system:**
- Janos Technology Ninox 3 ~12  $\mu\text{m}$  lens
  - SE-IR CamIRa software, Closed cycle dewar, Camera Head electronics
  - Extended (plate) Blackbody source



# Images from 320x256 FPAs



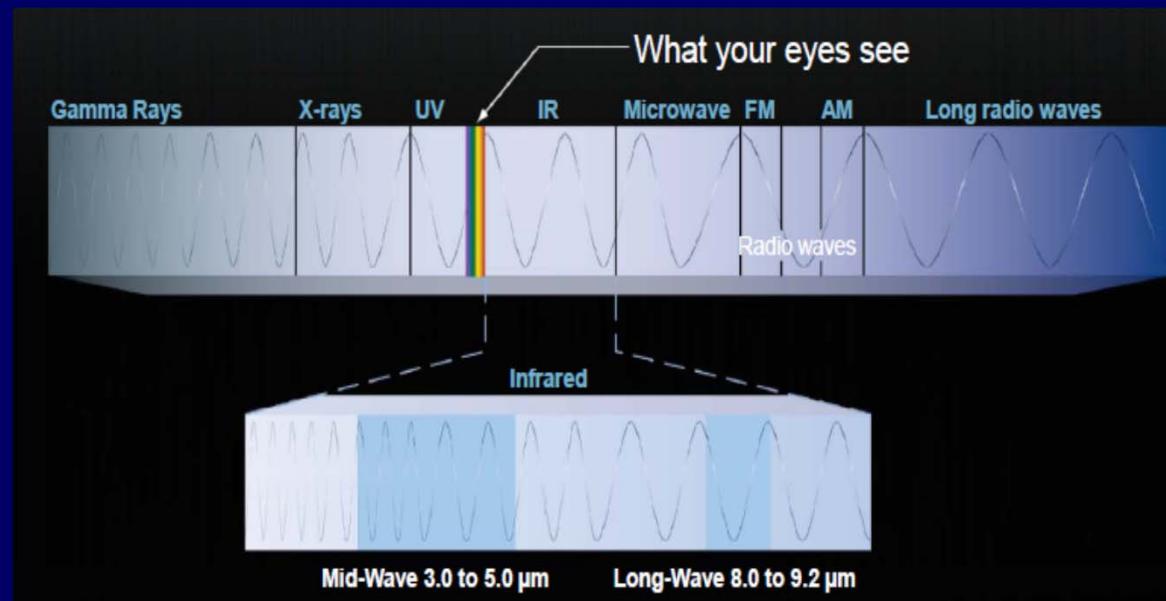
Superlattice FPAs

Quantum Dot FPAs



# Outline

## ➤ *Type II Strain Layer Superlattices*



# Band-gap Engineering of Type-II Semiconductor Active Layers

## 0.17 InAs/(In)GaSb Type II Strain Layer Superlattice Detectors

**E Plis**, University of New Mexico, Albuquerque, NM, USA

**J B Rodriguez**, Université Montpellier 2, Montpellier, France

**S Krishna**, University of New Mexico, Albuquerque, NM, USA

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InAs / 8 ML GaSb

Wave function  
function

8ML) InAs(8ML) GaSb(8ML)

### Detectors Based on InAs/(In)GaSb SLS

#### Figures of Merit for IR Detectors

External QE ( $\eta$ ?)

Responsivity (R)

Noise equivalent power

Specific detectivity ( $D^*$  and  $D^{**}$ )

Response time,  $\tau$

Dynamic impedance of the detector at zero bias ( $R_0 A$ )

Noise equivalent temperature difference

Minimum resolvable temperature difference

Linearity of response and dynamic range

Cross-talk between detector elements of FPA

Modulation transfer function

#### Advantages of SLS for IR Detection

Application of InAs/(In,Ga)Sb Detectors for MWIR, LWIR, and VLWIR Detectors

MWIR detection

LWIR detection

VLWIR detection

#### Multicolor Detectors

Multicolor detection using HgCdTe detectors

Multicolor detection using QWIP detectors

Multicolor detection using SLS detectors

#### Limitations of SLS Technology

New SLS Architectures

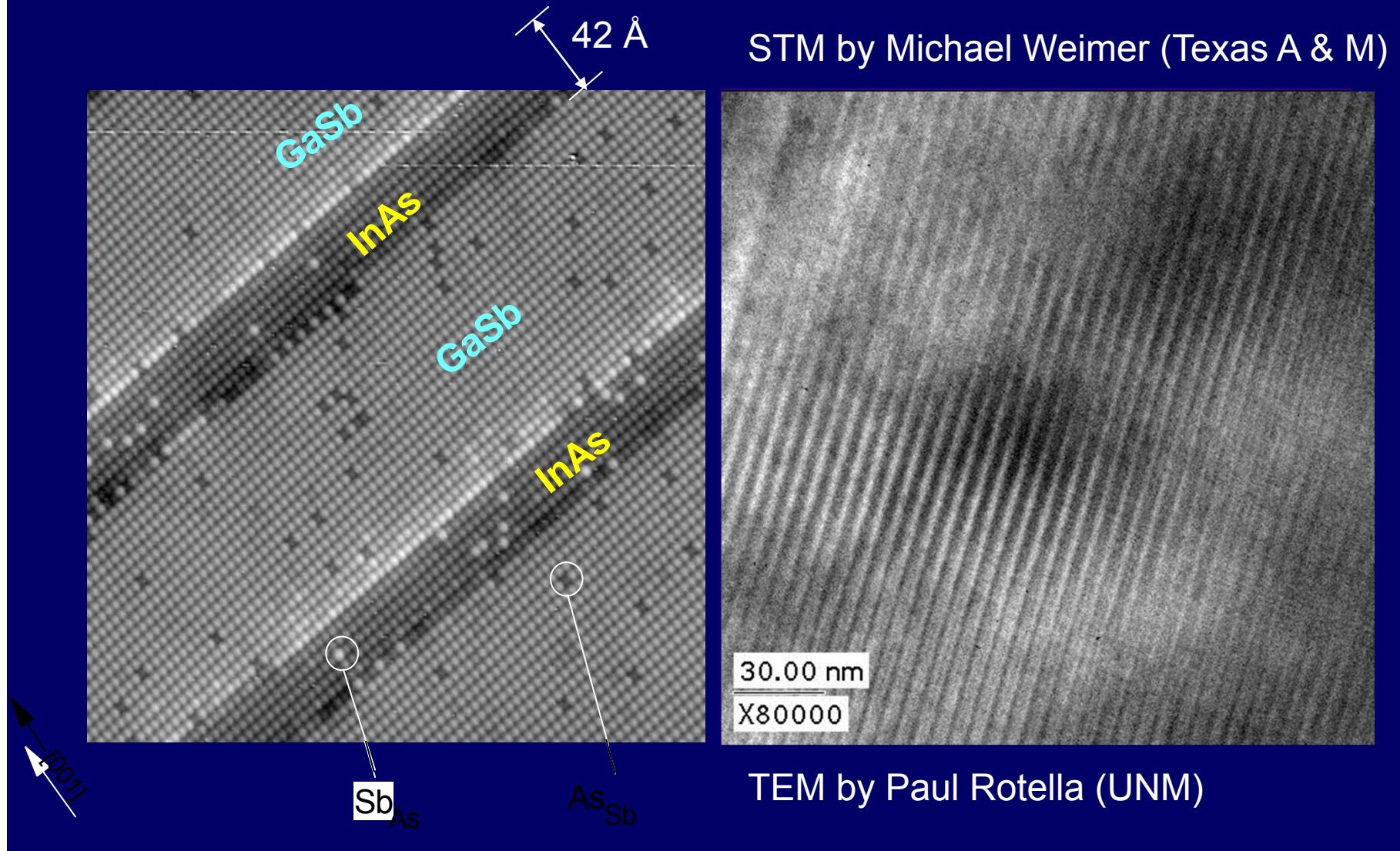
#### Conclusion

- 0.17.1 Introduction
  - 0.17.1.1 Semiconductors in IR Detection
- 0.17.2 Superlattices
  - 0.17.2.1 Principles of Quantum Confinement
  - 0.17.2.2 Types of Superlattices
- 0.17.3 InAs/(In)GaSb SLSs
  - 0.17.3.1 Historical Background
  - 0.17.3.2 Different Approaches to Bandstructure Modeling of SLS
    - 0.17.3.2.1  $k \cdot p$  method
    - 0.17.3.2.2 Superlattice empirical pseudopotential method
    - 0.17.3.2.3 Atomistic empirical pseudopotential method
    - 0.17.3.2.4 Empirical tight-binding method
  - 0.17.3.3 Growth of InAs/(In, Ga, Al)Sb SLSs
    - 0.17.3.3.1 Material uniformity
    - 0.17.3.3.2 Growth temperature
    - 0.17.3.3.3 Interfaces
    - 0.17.3.3.4 Strain compensation
    - 0.17.3.3.5 Adjustment of growth rate and arsenic incorporation
  - 0.17.3.4 Material Parameters for InAs/(Ga,In)Sb SLS
    - 0.17.3.4.1 Carrier lifetimes
    - 0.17.3.4.2 Auger coefficient
    - 0.17.3.4.3 Background carrier concentration
    - 0.17.3.4.4 Diffusion length
    - 0.17.3.4.5 Refractive index
    - 0.17.3.4.6 Electronic effective mass

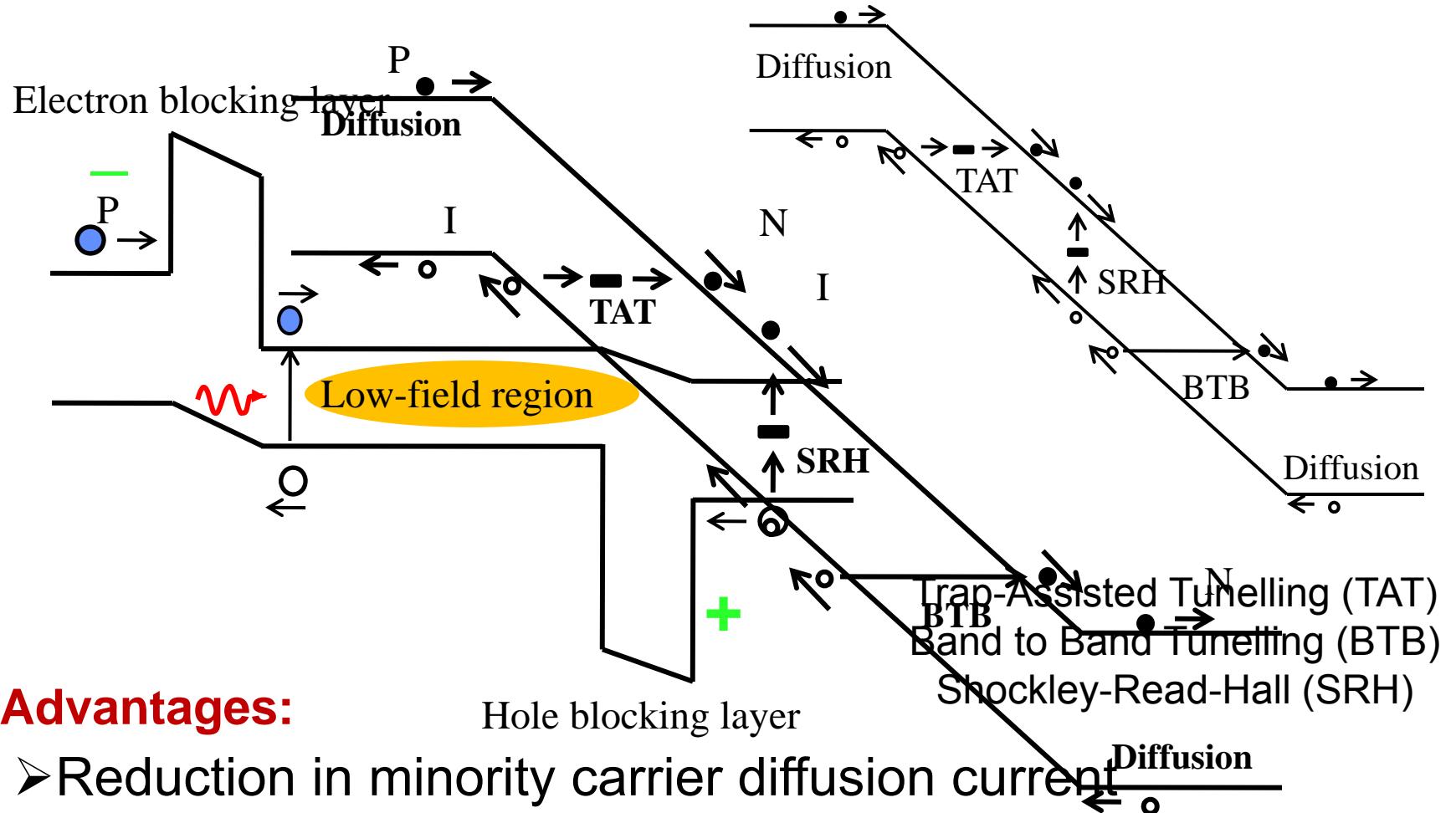


# Epitaxial Growth of Type-II Strain Layer Superlattices

Growth by Solid Source MBE System at CHTM by Kaspi



# Unipolar Barrier Diode (PbI<sub>6</sub>N)

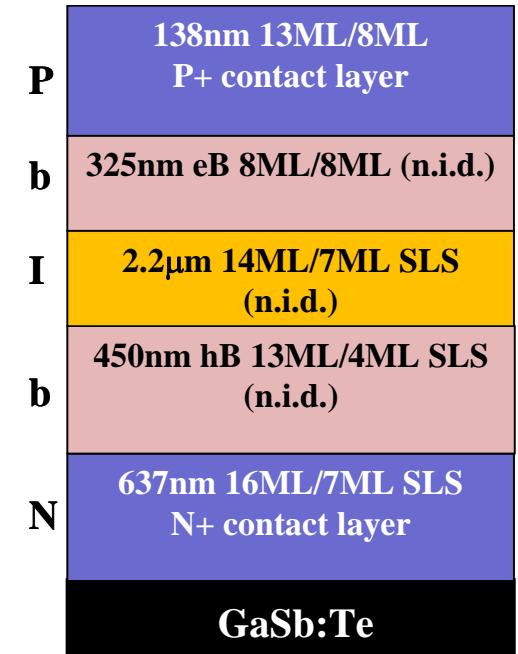
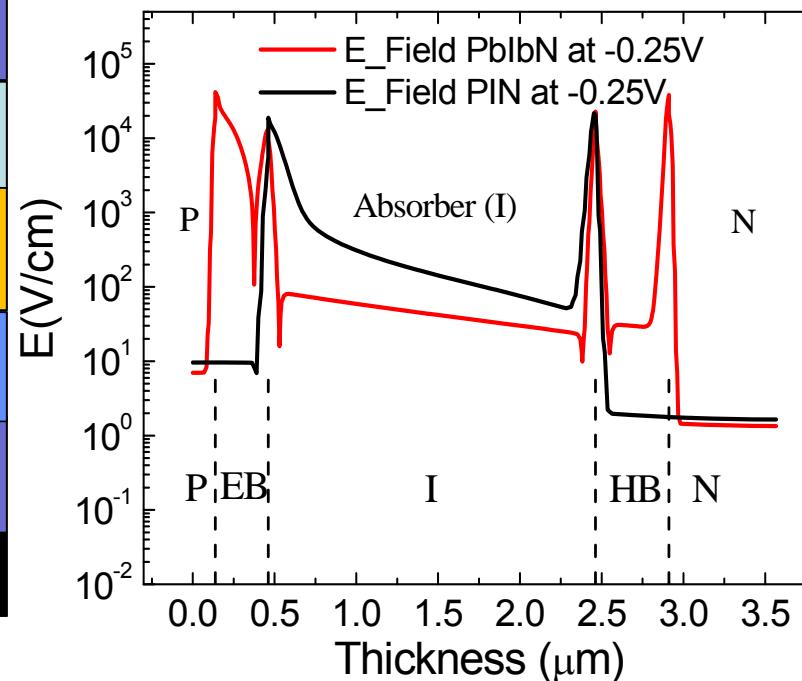
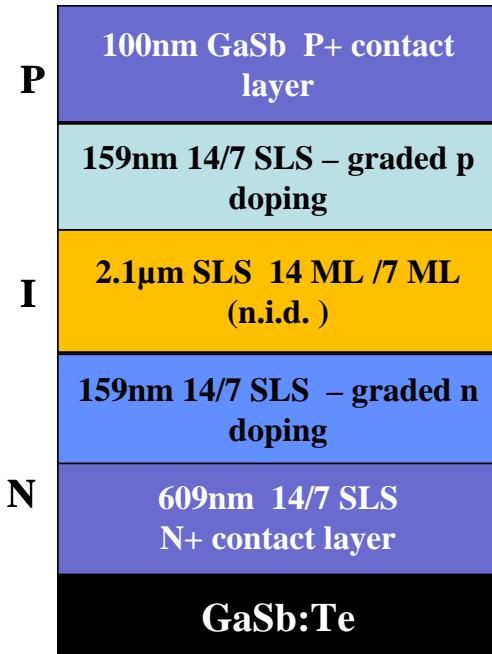


## Advantages:

- Reduction in minority carrier diffusion current
- Reduction in tunneling
- Reduction in SRH currents

PIN diode under reverse bias operation

# Unipolar Detector Design



Band offsets and bandgaps obtained from Semi-Empirical Pseudopotential Method and fed to Sentaurus T-CAD for further calculations

**Significant reduction in field drop across absorber region**

<sup>1</sup>Gregory C. Dente and Michael L. Tilton, J. Appl. Phys. 86, 1420 (1999)

<sup>2</sup><http://www.synopsys.com/Tools/TCAD/Pages/default.aspx>

# Improved PbIbN Design

**5/8 SLS P+ contact Layer (38 P) 130nm**

**EB 7ML GaSb/4ML AlSb SLS (45 Periods) (149nm)**

**14ML InAs/7ML GaSb SLS (1.94 $\mu$ m thickness) (p1e16) (300 P) (both layers dopes p-type)**

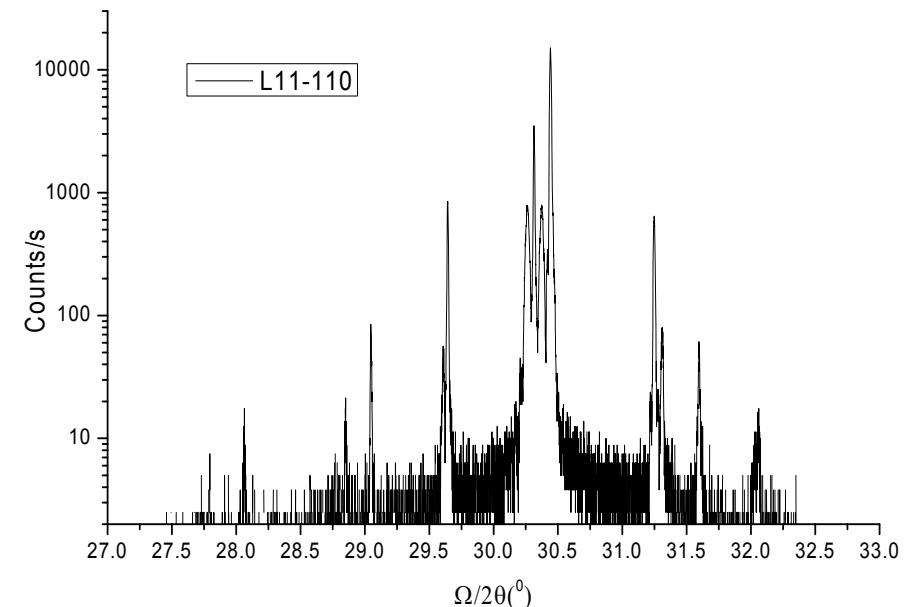
**45P (16ML InAs/4ML AlSb) (n.i.d) (275nm)**

**N+ Contact Layer 9/4 SLS (200 Periods)(800nm)**

**GaSb:Te  
2" wafer**

*Not previously reported*

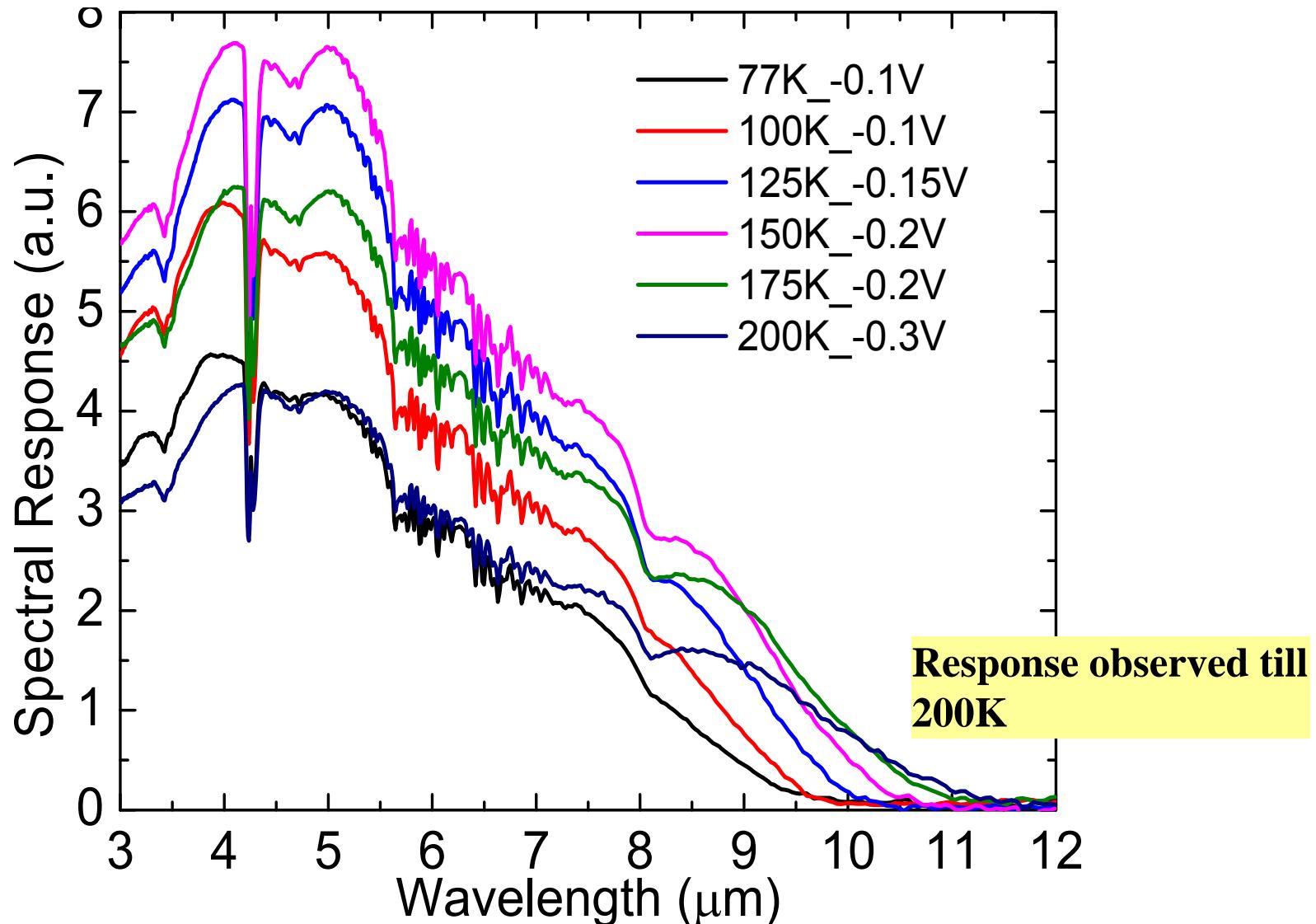
- Optimized barrier height to reduce operating bias
- Increased barrier height using AlSb



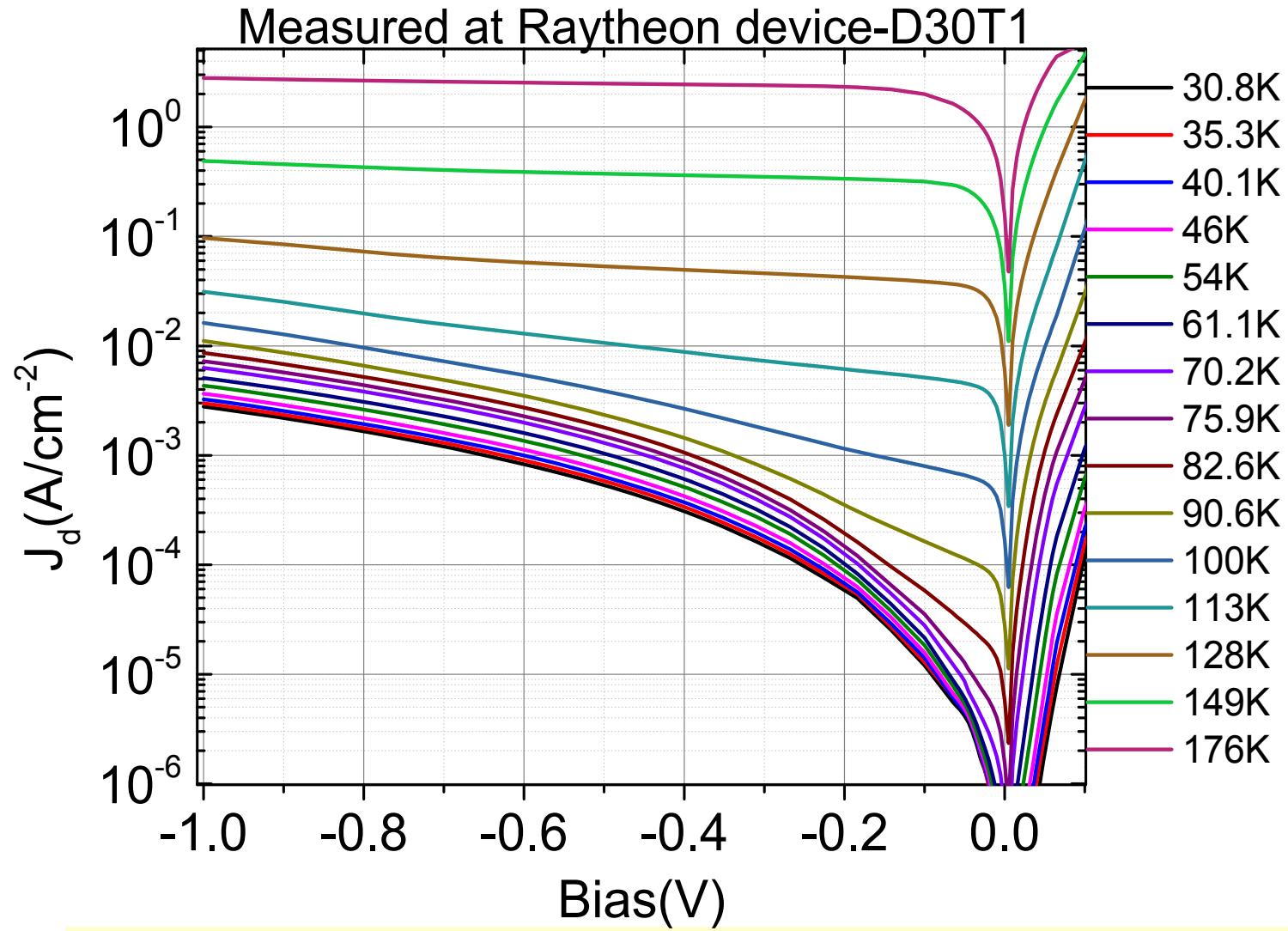
**L11-110**



# Spectral Response

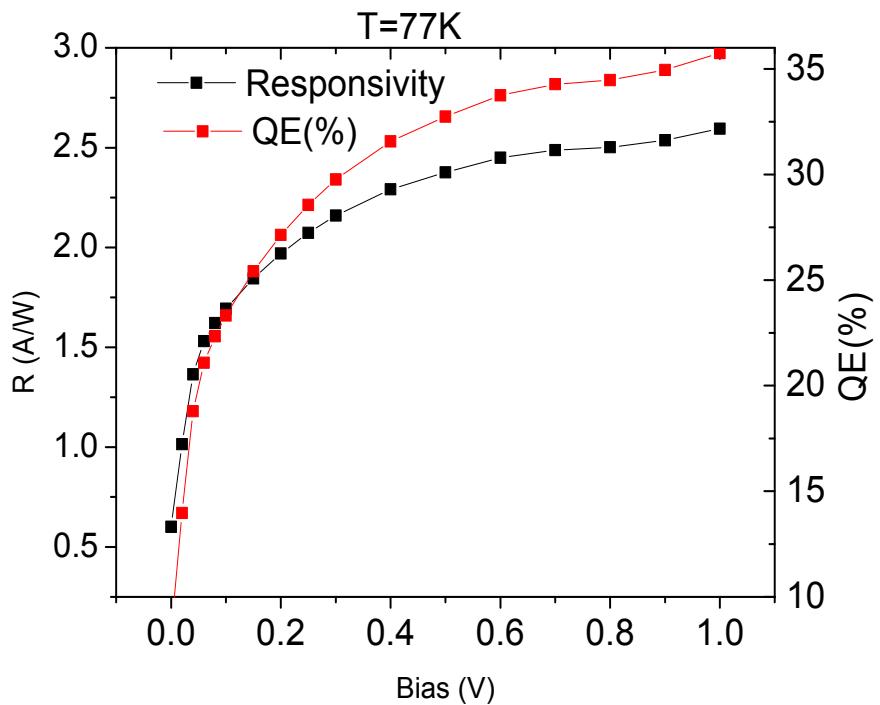
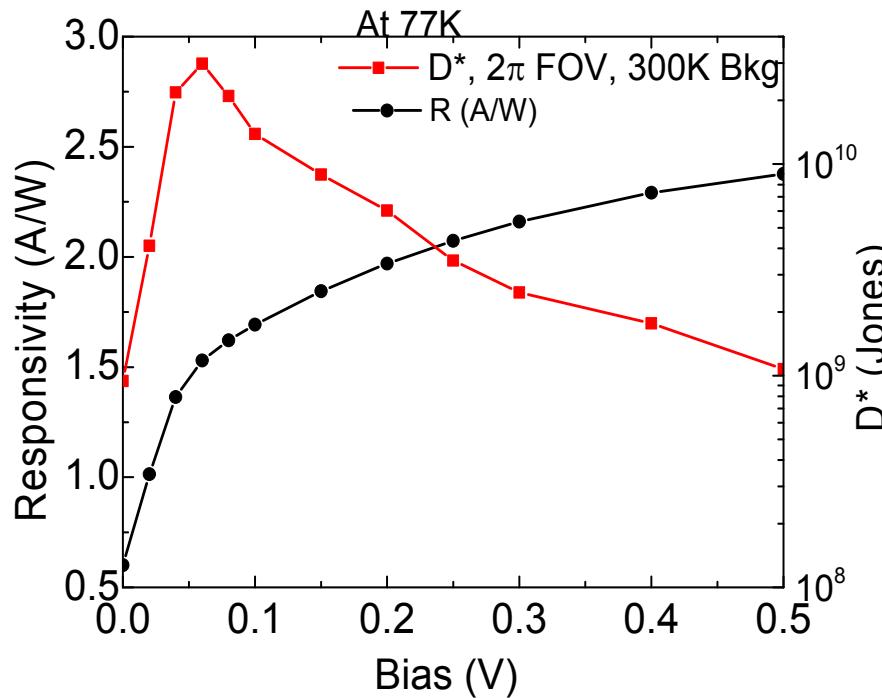


# Dark Current Measurements at RVS



$J_d = 1.6 \times 10^{-5}$  A/cm<sup>2</sup> at 76K at -60mV (bias for highest SNR)

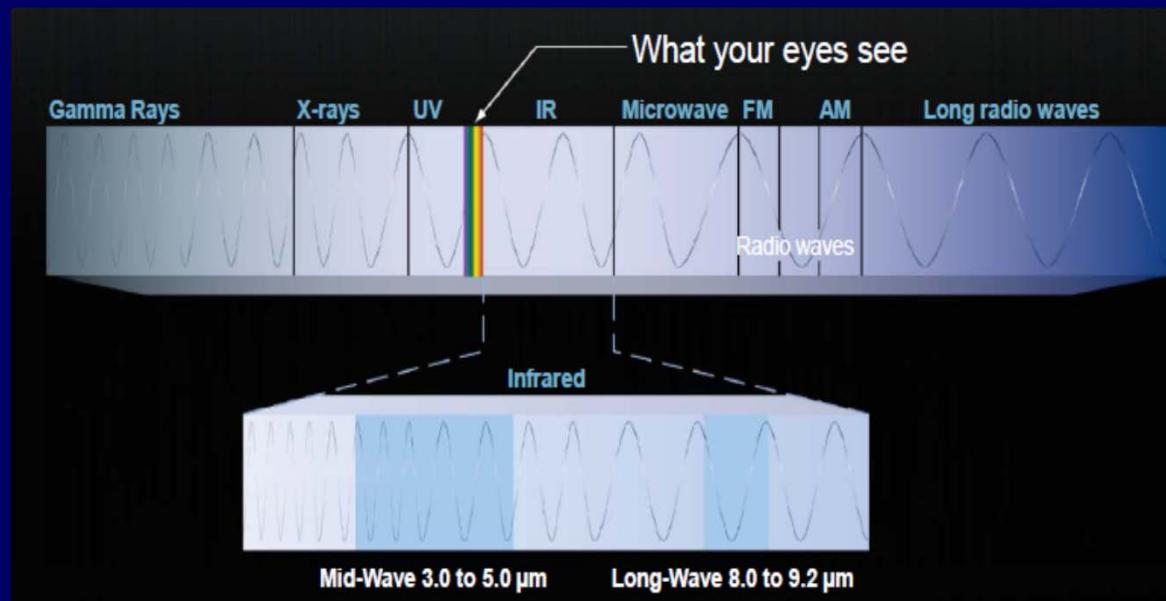
# Quantum Efficiency



- Single pass QE=23% at 60 mV without AR coating
- Detectivity calculated with noise measurements and NOT from dark current data
- Signal measured using 8.4  $\mu\text{m}$  long pass filter
- Devices are at RVS for independent evaluation

# Outline

## ➤ *Quantum Dots in a Well Detectors*



# Self-Assembled Growth of Quantum Dots

Frank-van der Merwe  
2d layer by layer



Stranski-Krastanow  
Initial 2d growth,  
Later 3d island growth

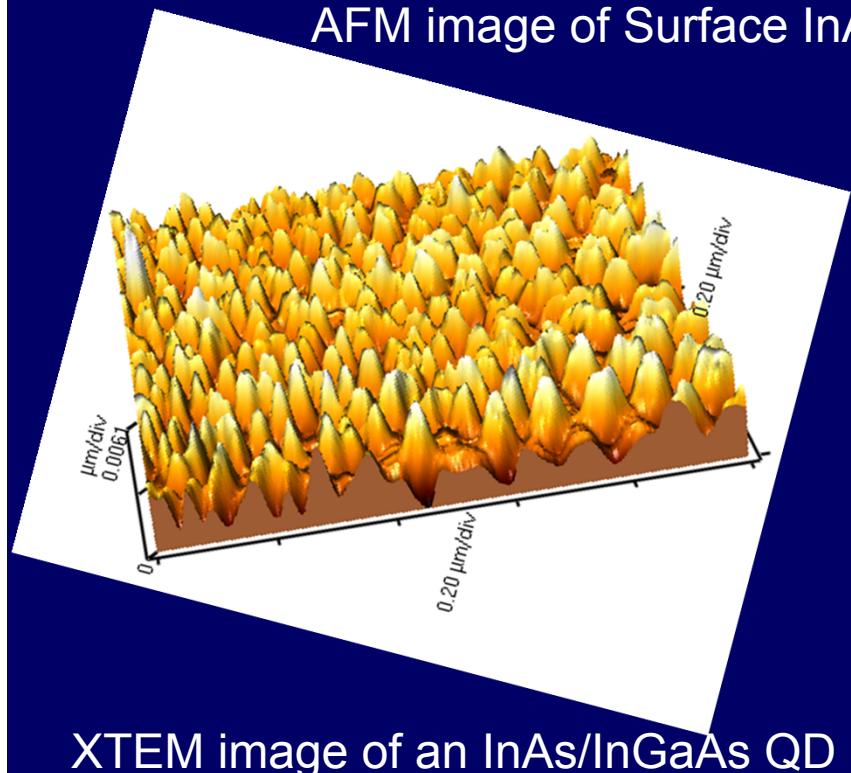


Vollmer-Weber 3d  
island growth

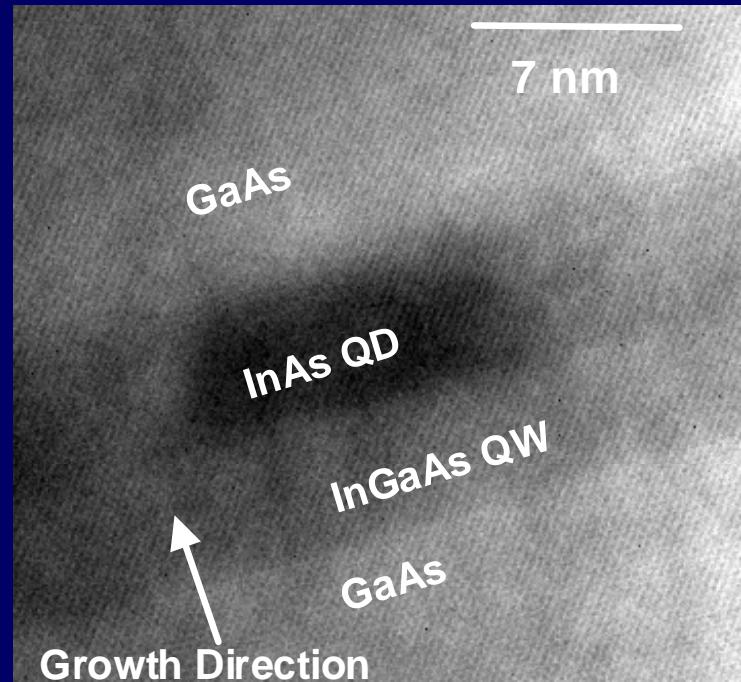


Increasing Strain

AFM image of Surface InAs QDs



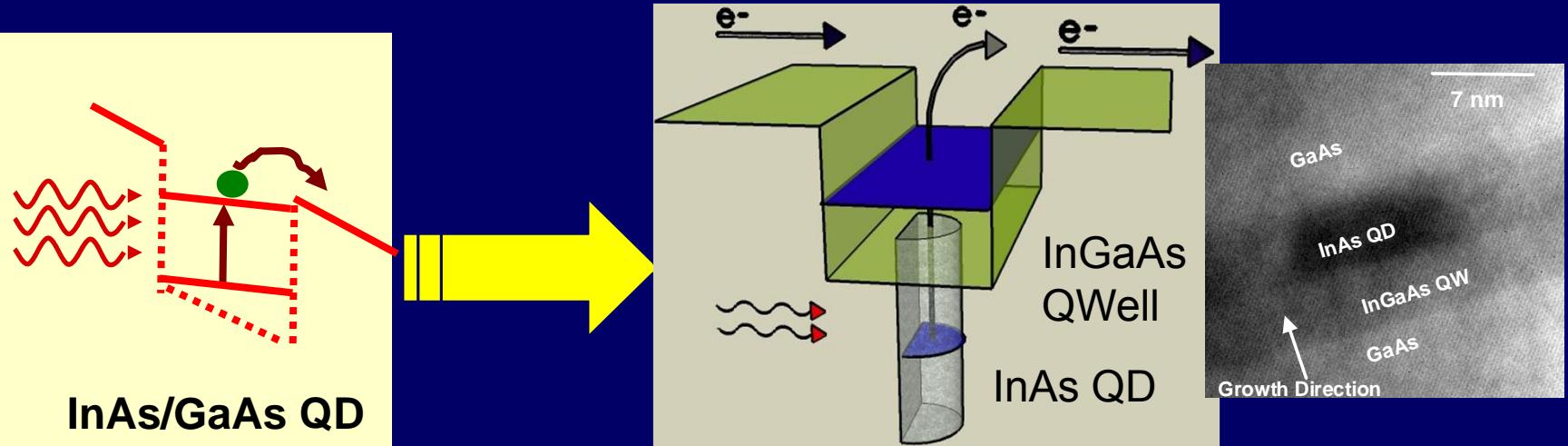
TEM by P. Rotella



# InAs/InGaAs Dots in a Well Detectors

## Band-structure Engineering of QD Detectors

- Placing the dots in an InGaAs well (DWELL) is expected to lead to reduced thermionic emission → lower dark current → higher operating temperature
- The operating wavelength and nature of transition can be tailored by varying the width and the composition of the InGaAs QW
- Tailoring asymmetry in bandstructure for exploiting QCSE
- Novel Physics: transitions between carriers with different degrees of confinement



Krishna et al, *Appl. Phys. Lett.*, 80, 3898, 2002

Raghavan et al, *Appl. Phys. Lett.*, 81, 1369, 2002

\* Krishna et al, *IEEE Circuits and Devices*, p.14, Jan. 2002; *Appl. Phys. Lett.*, 79, 21, 2001.



# InAs/InGaAs Dots in a Well Detectors

## Bias and temperature dependence of dots-in-a-well infrared photodetectors

L. Höglund,<sup>1,a)</sup> P. O. Holtz,<sup>2</sup> H. Pettersson,<sup>3</sup> C. Ås  
S. Smuk,<sup>4</sup> E. Petrini,<sup>1</sup> and J. Y. Andersson<sup>1</sup>

<sup>1</sup>*Acree AB, Electrum 236, S-16440 Kista, Sweden*

<sup>2</sup>*Department of Physics, Chemistry and Biology (IFM), Lin*

<sup>3</sup>*Center for Applied Mathematics and Physics, Halmstad Un  
Sweden and Solid State Physics and the Nanometer Structu  
S-22100 Lund, Sweden*

<sup>4</sup>*IRnova, Electrum 236, S-16440 Kista, Sweden*

(Received 11 July 2008; accepted 10 August 2008; pu

## Spectral function of InAs/InGaAs qu using Green's function

M. A. Naser, M. J. Deen,<sup>a)</sup> and D. A. Thompson  
*Department of Electrical and Computer Engineering, M  
West, Hamilton, Ontario L8S 4K1, Canada*

(Received 11 July 2006; accepted 22 August 2006;

## Energy level structure and electron relaxation times in InAs/In<sub>x</sub>Ga<sub>1-x</sub>As quantum dot-in-a-well structures

P. Aivaliotis,<sup>a)</sup> S. Menzel, E. A. Zibik, J. W. Cockburn, and L. R. Wilson<sup>b)</sup>  
*Department of Physics and Astronomy, The University of Sheffield, Sheffield S3 7RH, United Kingdom*

M. Hopkinson  
*EPSRC National Centre for III-V Technology, The University of Sheffield, Sheffield S1 3JD, United  
Kingdom*

(Received 5 October 2007; accepted 1 November 2007; published online 17 December 2007)  
PHYSICAL REVIEW B **78**, 115320 (2008)

## Gain and recombination dynamics in photodetectors made with quantum nanostructures: The quantum dot in a well and the quantum well

B. Movaghari, S. Tsao, S. Abdollahi Pour, T. Yamanaka, and M. Razeghi

*Center for Quantum Devices, Electrical Engineering, and Computer Science, Northwestern University, Evanston, Illinois 60208, USA*  
(Received 1 May 2008; revised manuscript received 30 July 2008; published 23 September 2008)

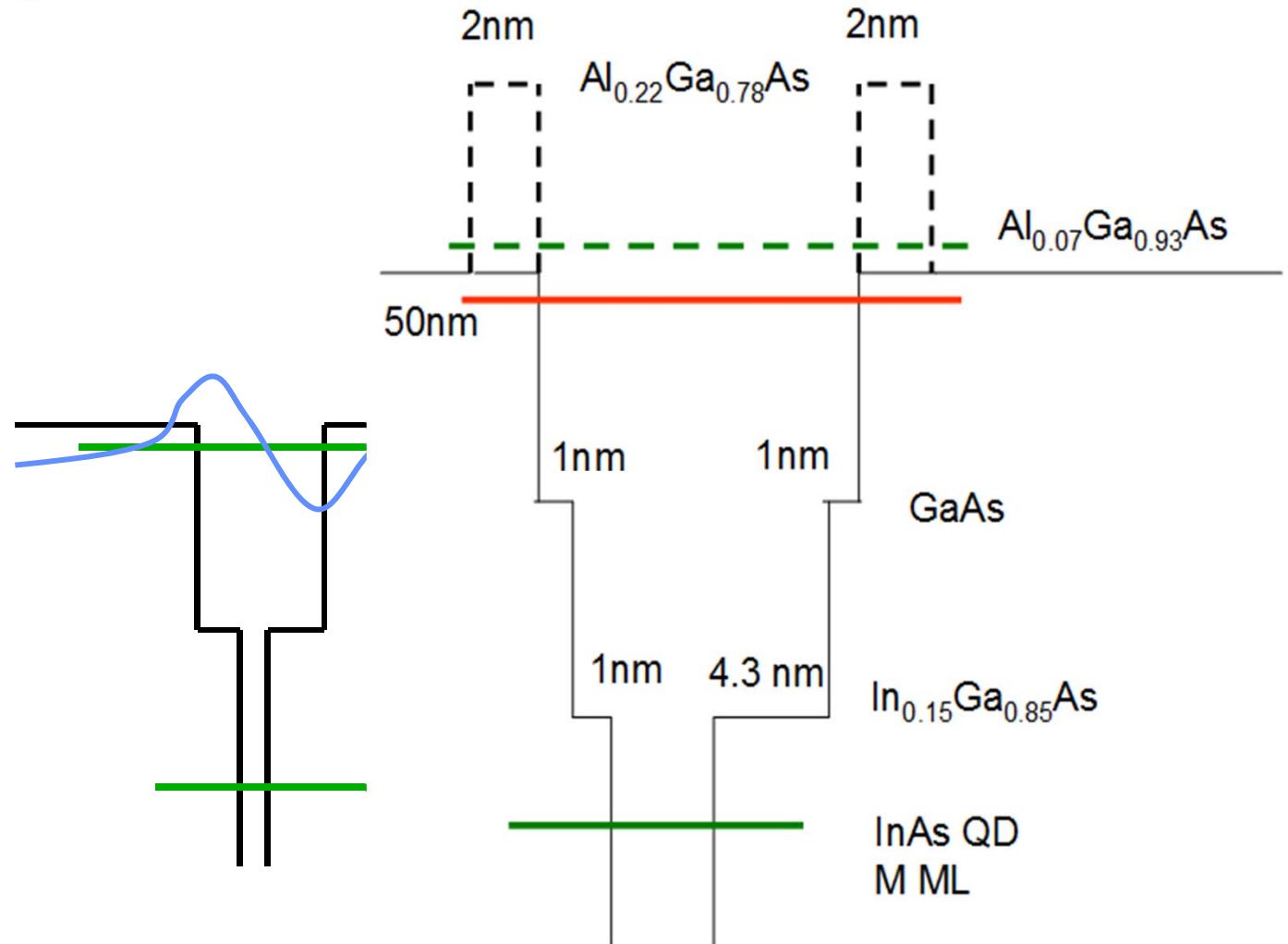
### • Various Research Groups are now using DWELLS

- IR Nova/Linkoping University (Sweden)
- Wilson/David Group (Sheffield University)
- Jagadish Group (Australian National University)
- J.Deen Group (McMaster University)
- Razeghi Group (Northwestern University)
- Wang Group (Taiwan)
- Gunapala Group (NASA JPL)
- Lu Group (UMass)

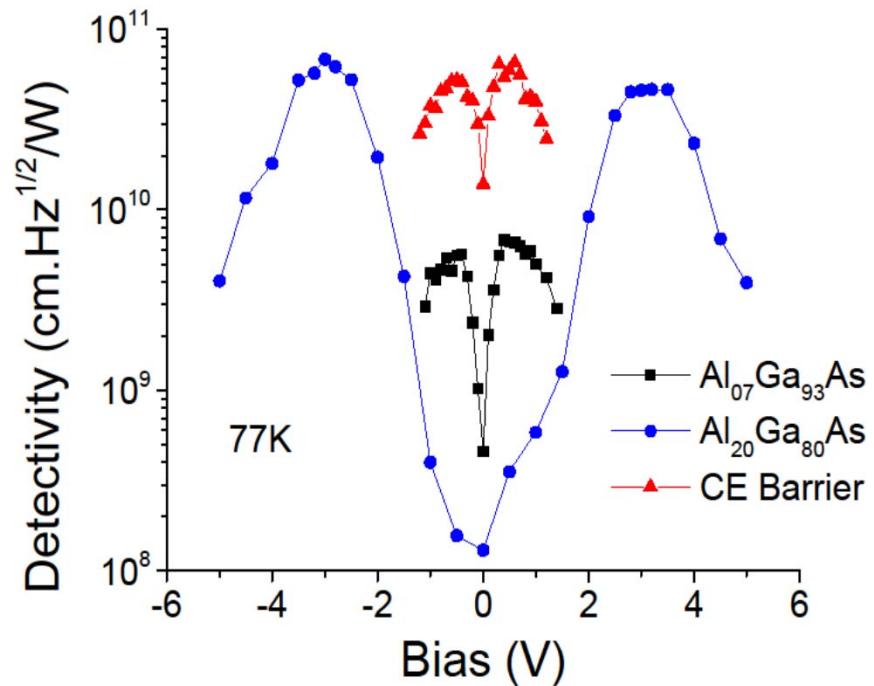
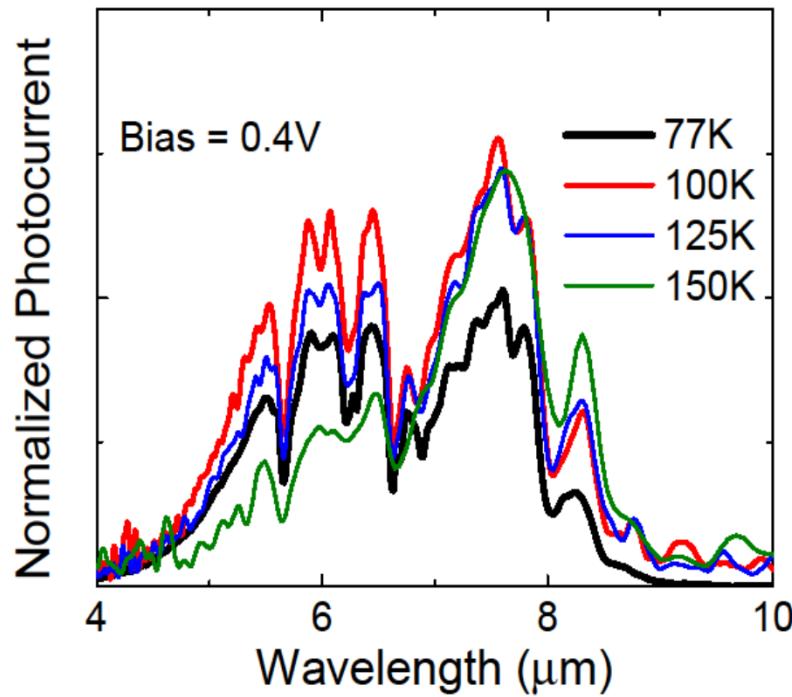
640 × 512 Pixels Long-Wavelength Infrared (LWIR)  
Quantum-Dot Infrared Photodetector (QDIP)  
Imaging Focal Plane Array

Sarith D. Gunapala, Sumith V. Bandara, Cory J. Hill, David Z. Ting, John K. Liu, Sir B. Rafol,  
Edward R. Blazejewski, Jason M. Mumolo, Sam A. Keo, Sanjay Krishna, Y.-C. Chang, and Craig A. Shott

# Confinement Enhancing DWELL Design



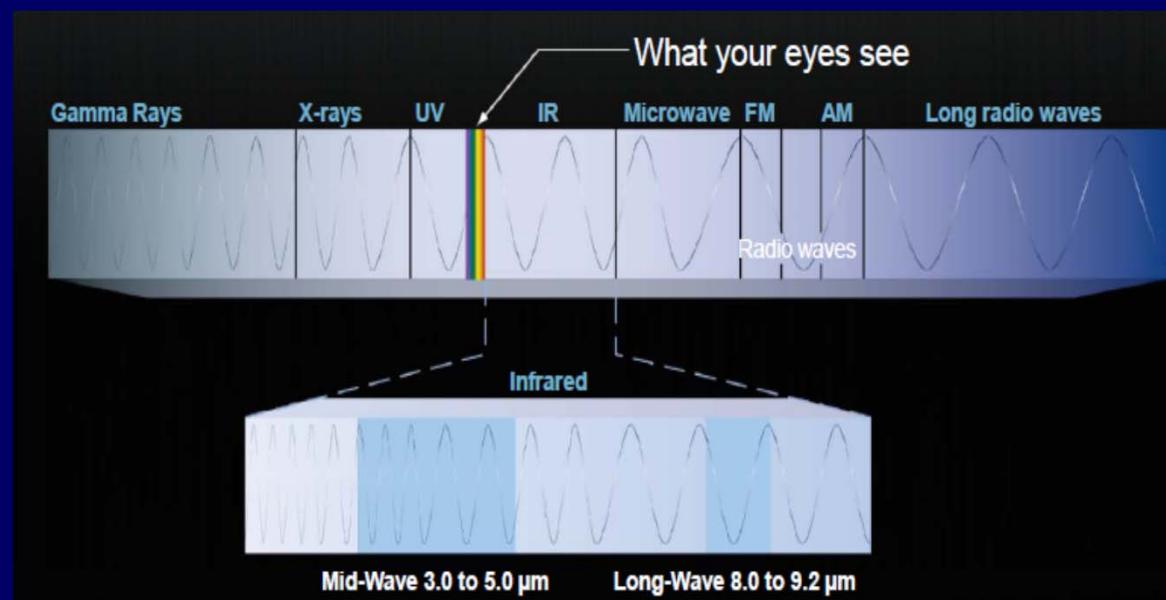
# Spectral Response and Radiometric Characterization



- Response observed till 150K
- Detectivity of  $6\text{e}11 \text{ cm Hz}^{1/2}/\text{W}$  at 0.4V (77K)
- High detectivity at low bias

# Outline

## ➤ 4<sup>th</sup> Gen Imagers: The Infrared Retina





# Looking Ahead: Vision for 4<sup>th</sup> Gen

## *Figer Questions !*

1. What are the problems with the current generation of IR detectors?
2. What are the most interesting developments that you would like to see for your topic over the next ten years?
3. What are the biggest challenges for developing relevant technology over the next ten years?
4. What science breakthroughs could be enabled by this technology over the next ten years?



# “Too Much Data” Problem



## SEEING PHOTONS

PROGRESS AND LIMITS OF VISUAL AND INFRARED SENSOR ARRAYS

*Committee on Developments in Detector Technologies*

*Standing Committee on Technology Insight  
—Gauge, Evaluate, and Review*

*Division on Engineering and Physical Sciences*

NATIONAL RESEARCH COUNCIL  
OF THE NATIONAL ACADEMIES

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Washington, D.C.  
[www.nap.edu](http://www.nap.edu)



FIGURE 2.1-2  
Autonomous Real-time Ground Ubiquitous Surveillance Imaging System

a modest degree of compression. For example, an ARGUS-IS-like system can produce up to 770 gigabits per second. The use of a Common Data Link (CDL) operating at 274 megabits per second would require compression ratios on the order of 2,800, far beyond the capabilities of lossless compression techniques.

**The bottleneck to decision making is the user in the loop**

# Multimodal Sensing

- *Present Day Infrared FPAs*
- *Mostly Single Color (Monitor Emissivity)*
- *Multispectral FPAs use either multiple FPAs or spinning filter wheel*
- *Cost Increases Dramatically*



2

Rehm et. al Electronic Letters, 42, 577 (2006)

<sup>3</sup>J. S. Tyo et.. al Applied Optics, 45 (2006)

# Looking Ahead: Vision for 4<sup>th</sup> Gen

All Pixels look the same in present day systems

The **Fourth Generation** Infrared Imaging Systems should have the following information encoded at the **pixel level**

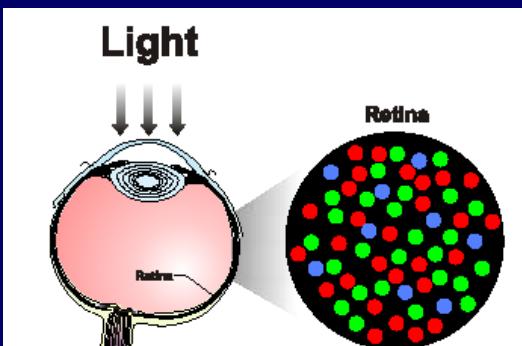
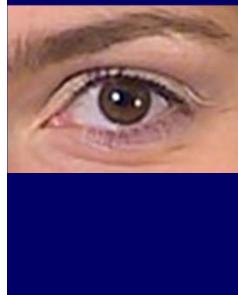
**Spectral Content**

**Polarization Information**

**Dynamic Range (or gain)**

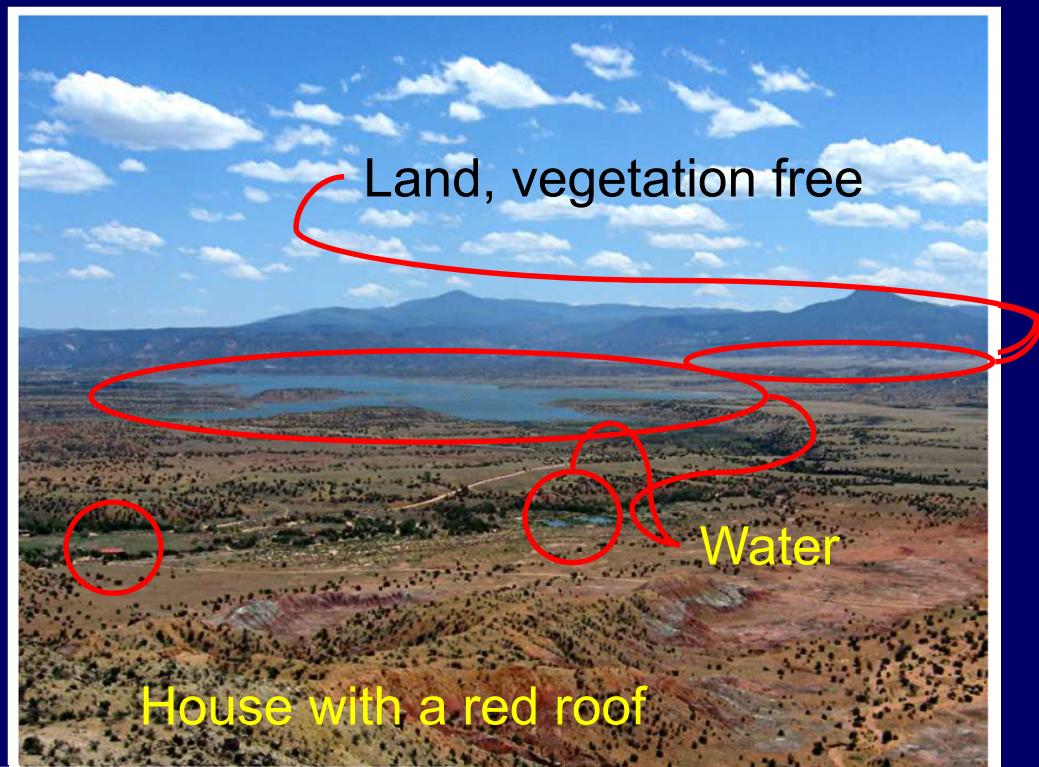
**Phase Sensitive Detection**

**Reduced Data Bandwidth**

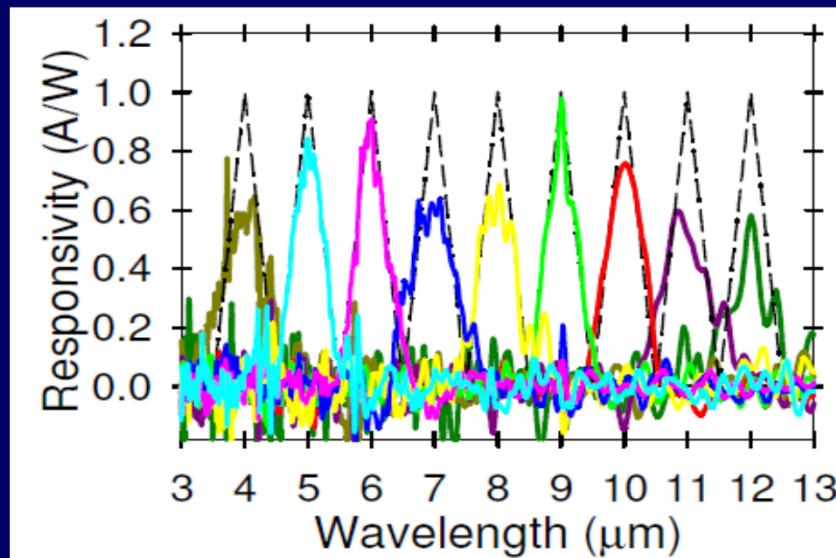
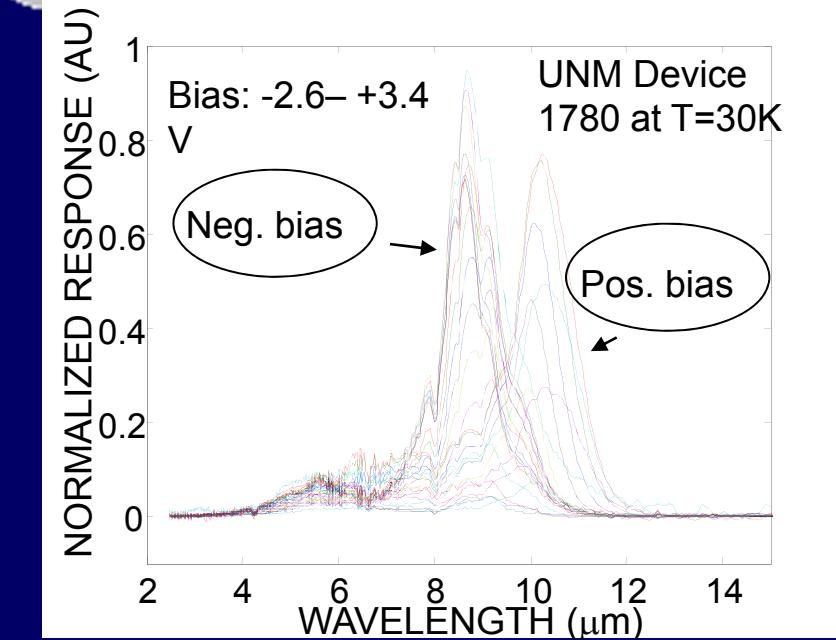


(12) **United States Patent**  
Krishna et al.

(10) **Patent No.:** US 8,071,945 B2  
(45) **Date of Patent:** Dec. 6, 2011



# Spectrally Tunable Smart Sensors



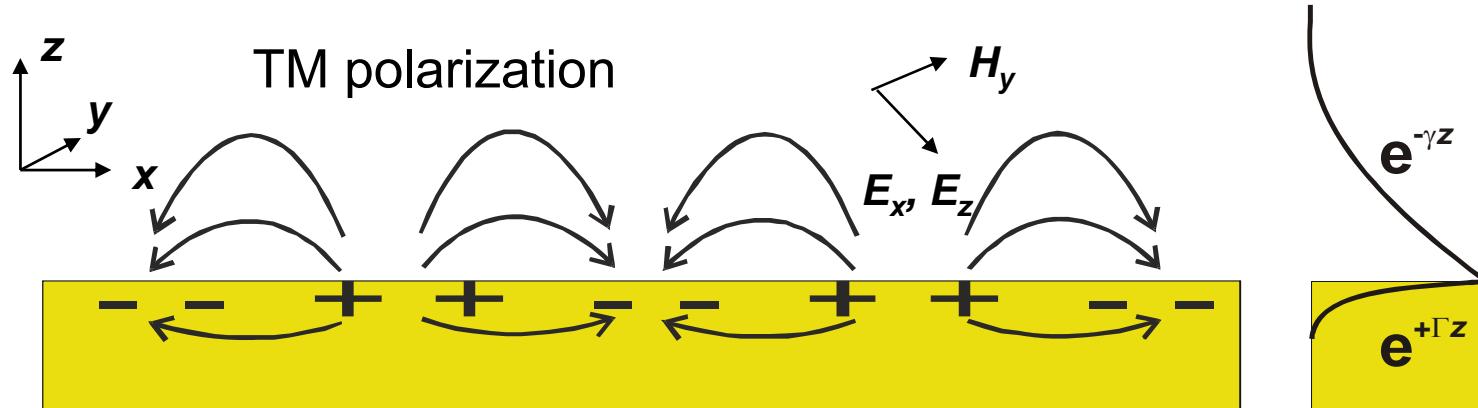
**Our idea is based on a *bias-tunable* Quantum Dot Infrared Photodetector (QDIP)**

- In an asymmetric well allow the spectral response to vary as the bias voltage is changed
- The spectral diversity is then passed through a post-processing algorithm to achieve (~) arbitrary spectral response
- A single FPA can be used for several different spectral imagery missions  
**software reconfigurable!**

← **Multicolor Response using different bias combinations**

University of Sheffield/UNM Collaboration

# SURFACE PLASMA: WAVES BOUND TO METAL/DIELECTRIC INTERFACE



$$\text{Dielectric: } \vec{E}_a = E_0 \left\{ \hat{e}_x - \frac{i k_x}{\gamma} \hat{e}_z \right\} e^{-i k_x x} e^{-\gamma z} \quad \gamma = \sqrt{k_x^2 - \epsilon_d}$$

---

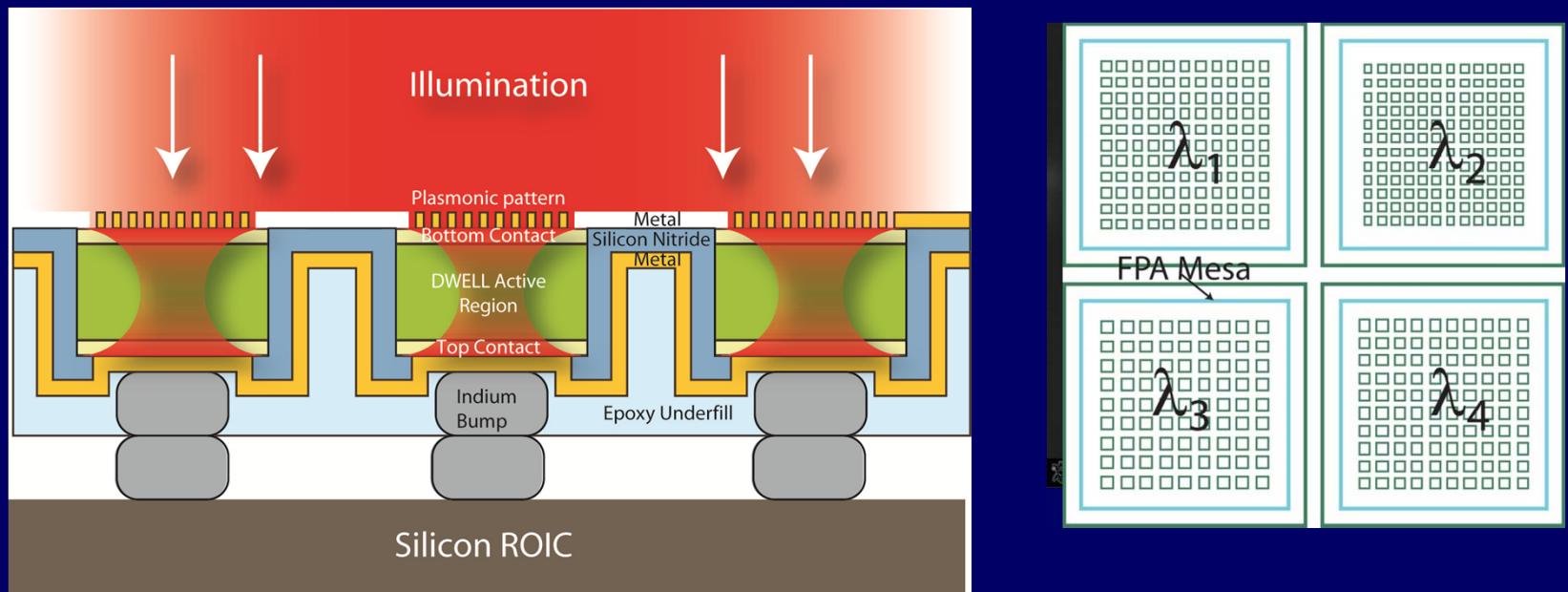

$$\text{Metal: } \vec{E}_m = E_0 \left\{ \hat{e}_x + \frac{i k_x}{\Gamma} \hat{e}_z \right\} e^{-i k_x x} e^{+\Gamma z} \quad \Gamma = \sqrt{k_x^2 - \epsilon_m}$$

Dispersionrelation:

$$\frac{\epsilon_d}{\gamma} + \frac{\epsilon_m}{\Gamma} = 0 \quad \gamma, \Gamma, \epsilon_d > 0 \Rightarrow \epsilon_m < 0$$

# Plasmonic Focal Plane Arrays

- Multispectral FPA
  - Integration of subwavelength patterns with illumination side of FPA.
  - Each pixel can detect different wavelength.
  - A thin semiconductor region between metals.



# Plasmonic QD Focal Plane Array

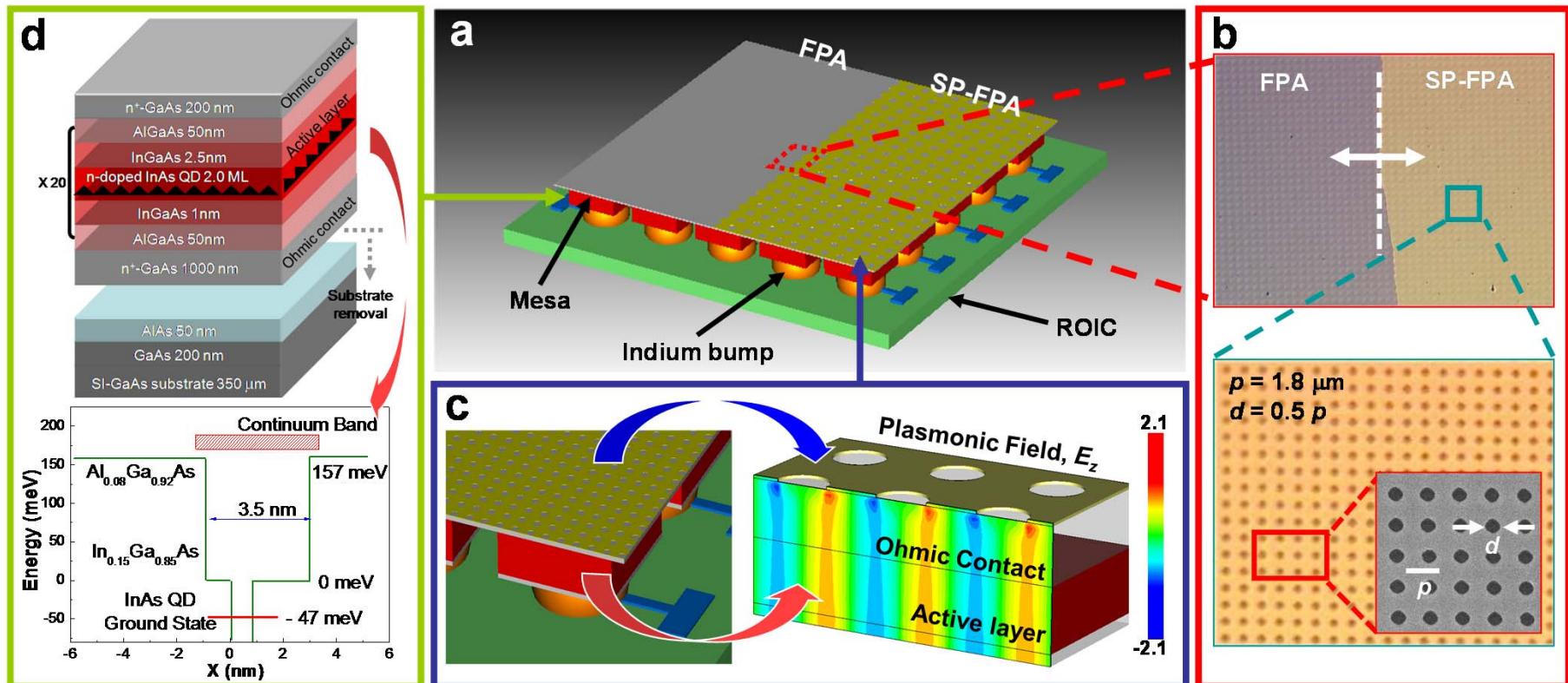
ARTICLE

Received 5 Jan 2011 | Accepted 17 Mar 2011 | Published xx xxx 2011

DOI: 10.1038/ncomms1283

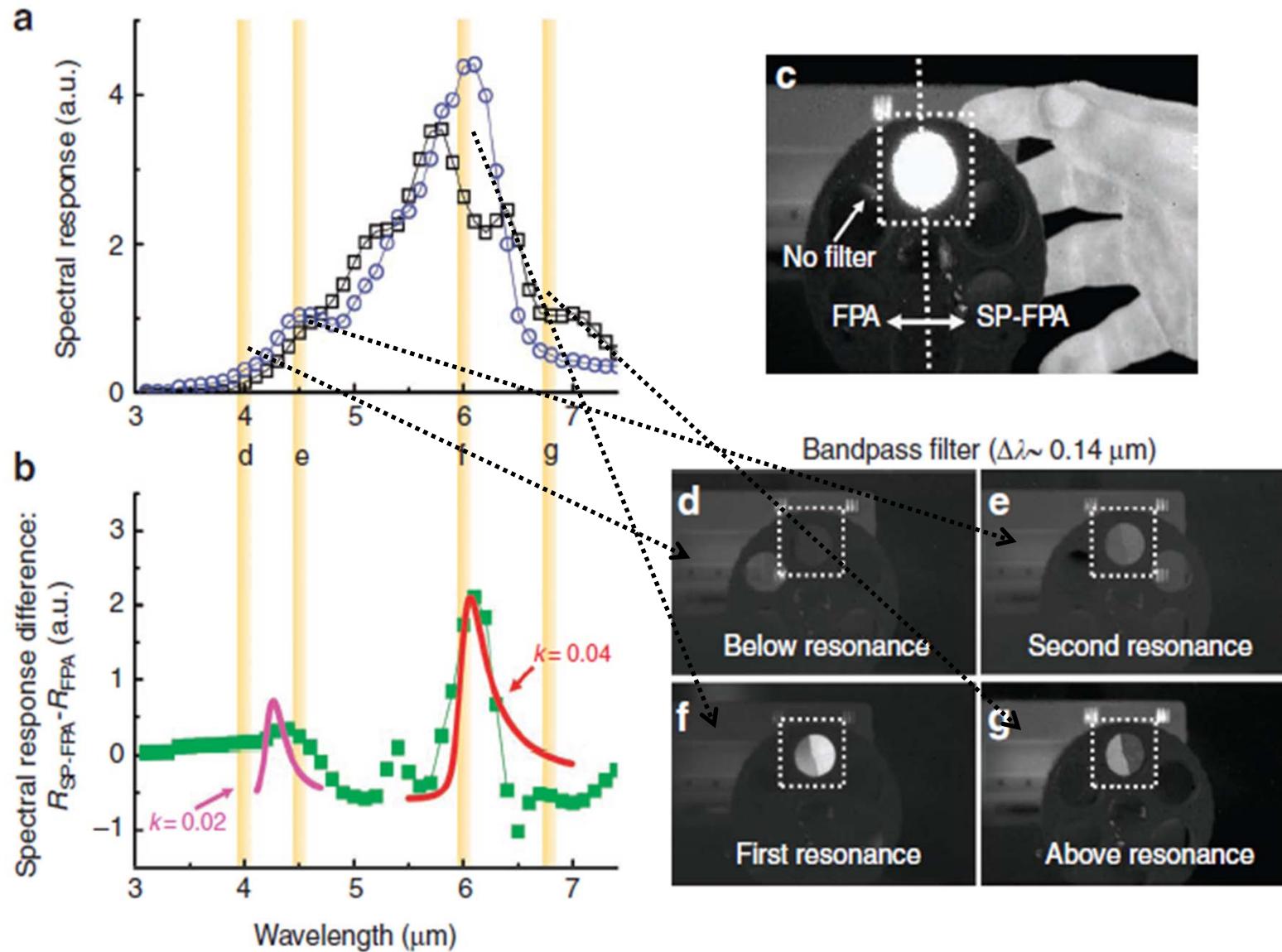
## A monolithically integrated plasmonic infrared quantum dot camera

Sang Jun Lee<sup>1,\*</sup>, Zahyun Ku<sup>2,\*†</sup>, Ajit Barve<sup>2</sup>, John Montoya<sup>2</sup>, Woo-Yong Jang<sup>2</sup>, S. R. J. Brueck<sup>2</sup>, Mani Sundaram<sup>3</sup>, Axel Reisinger<sup>3</sup>, Sanjay Krishna<sup>2</sup> & Sam Kyu Noh<sup>1</sup>

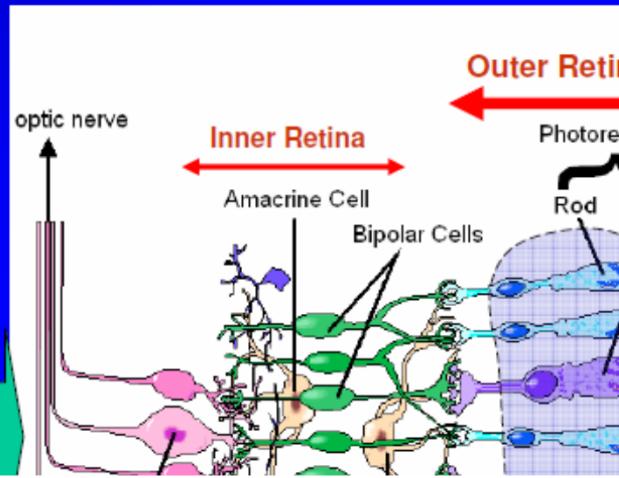
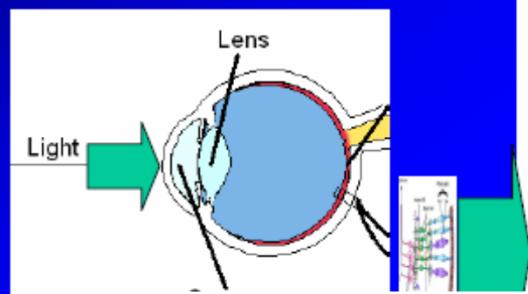


Collaboration with Prof. Brueck's group at UNM

# Spectral results Show ~ 2X Enhancement at SPW Resonance



# The Eye as an Imaging System



## **Eye strips images of all but bare essentials before sending visual information to brain, UC Berkeley research shows**

The eye as a camera has been a powerful metaphor for poets and scientists alike, implying that the eye provides the brain with detailed snapshots that form the basis for our rich experience of the world.

Recent studies at the University of California, Berkeley, however, show that the metaphor is more poetic than real. What the eye sends to the brain are mere outlines of the visual world, sketchy impressions that make our vivid visual experience all the more amazing.

"Even though we think we see the world so fully, what we are receiving is really just hints, edges in space and time," said Frank S. Werblin, professor of molecular and cell biology in the College of Letters & Science at UC Berkeley. Werblin is part of UC Berkeley's Health Sciences Initiative, a collaboration among researchers throughout the campus to tackle some of today's major health problems.

The brain interprets this sparse information, probably merging it with images from memory, to create the world we know, he said.

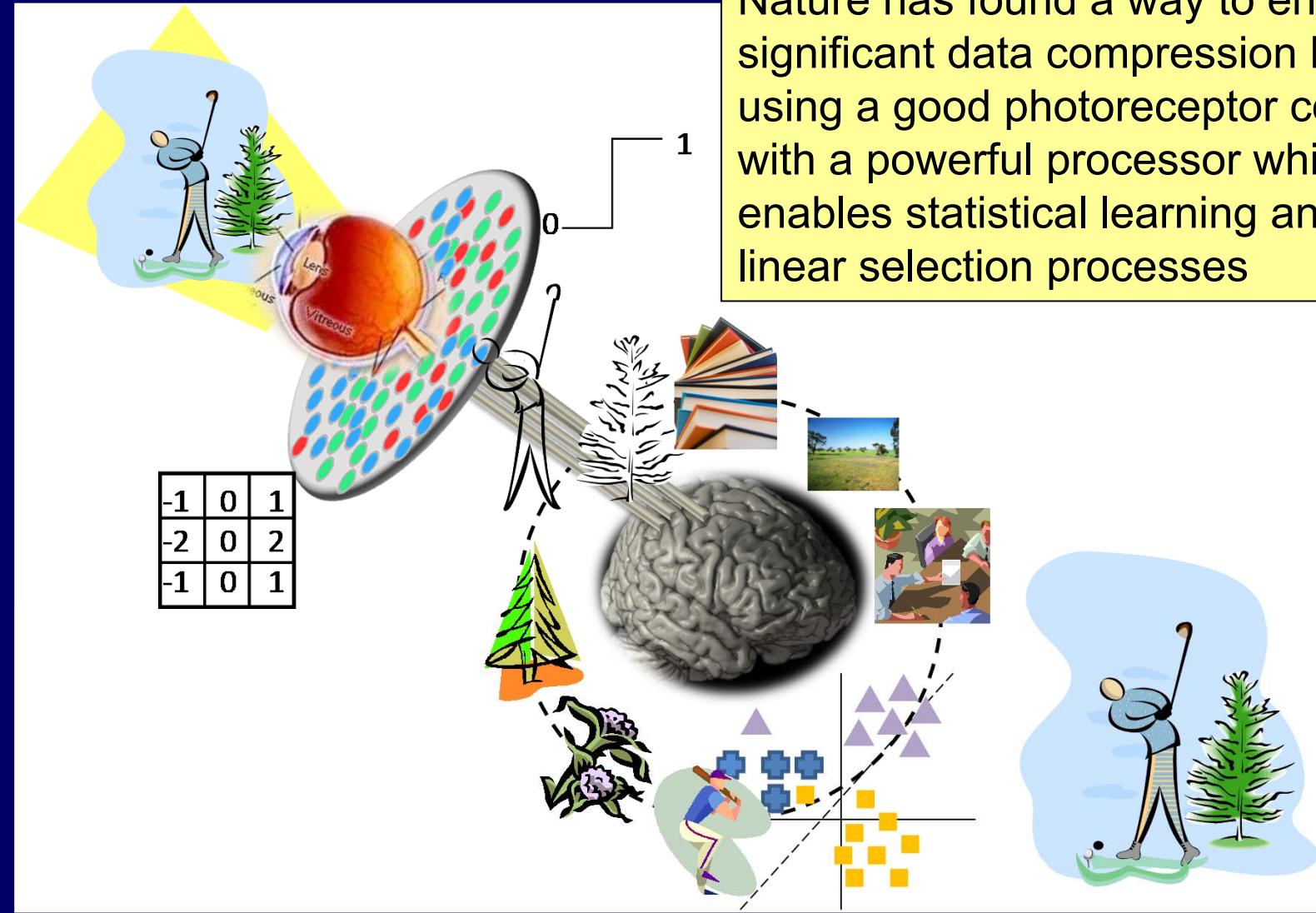
**Vertical interactions across ten parallel, stacked representations in the mammalian retina**

Botond Roska & Frank Werblin

**letters to nature**

Department of Molecular and Cell Biology, University of California at Berkeley,  
145 LSA, Berkeley, California 94720, USA

# Bioinspired Infrared Retina



Nature has found a way to enable significant data compression by using a good photoreceptor coupled with a powerful processor which enables statistical learning and non-linear selection processes

# New Functionality in Read Out Circuitry

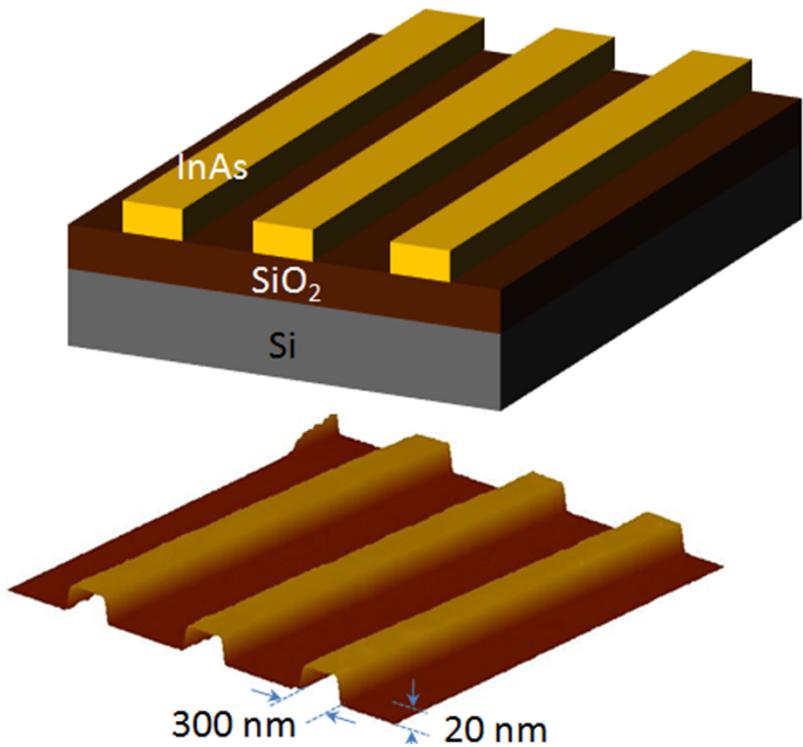
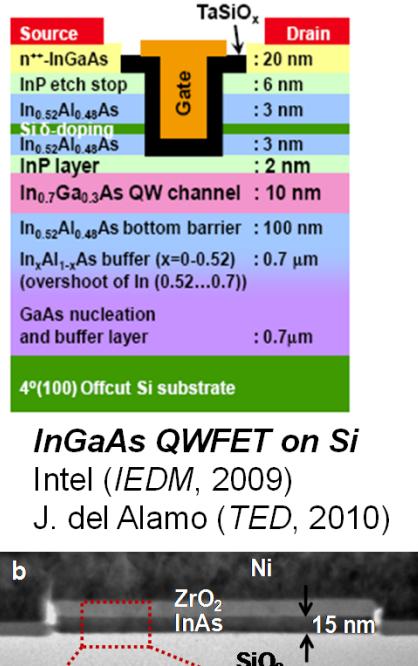
UNM

## Process Innovation

**Current – III-V QWFETs**  
require ***complex heteroepitaxial growth processes***

**XOI platform –**  
integration of ***ultra-thin*** III-V materials  
***on Si/SiO<sub>2</sub> by an epitaxial transfer process***, similar to wafer-bonding

**LETTER**



doi:10.1038/nature09541

## Ultrathin compound semiconductor on insulator layers for high-performance nanoscale transistors

Hyunhyub Ko<sup>1,2,3\*</sup>, Kuniharu Takei<sup>1,2,3\*</sup>, Rehan Kapadia<sup>1,2,3\*</sup>, Steven Chuang<sup>1,2,3</sup>, Hui Fang<sup>1,2,3</sup>, Paul W. Leu<sup>1,2,3</sup>, Kartik Ganapathi<sup>1</sup>, Elena Plis<sup>5</sup>, Ha Sul Kim<sup>5</sup>, Szu-Ying Chen<sup>4</sup>, Morten Madsen<sup>1,2,3</sup>, Alexandra C. Ford<sup>1,2,3</sup>, Yu-Lun Chueh<sup>4</sup>, Sanjay Krishna<sup>5</sup>, Sayeef Salahuddin<sup>1</sup> & Ali Javey<sup>1,2,3</sup>

# Summary and Conclusions

- Type II Superlattice and Quantum Dots as emerging IR technologies
- Plasmonic Detectors and Focal Plane Arrays
- Bioinspired Infrared Retina



**Superlattice FPAs**

**Quantum Dot FPAs**





# Future Outlook

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1. What are the problems with the current generation of IR detectors?

## **Data Overload**

2. What are the most interesting developments that you would like to see for your topic over the next ten years?

## **Bio-inspired Sensing**

3. What are the biggest challenges for developing relevant technology over the next ten years?

## **Integration of powerful hardware with intelligent algorithms**

4. What science breakthroughs could be enabled by this technology over the next ten years?

## **Intelligent Imaging for Biomedical Applications**



# Krishna Infrared Nanostructure Detector (KIND) Laboratory



**Summer 2011 ~\$14M in external funding since 2001**

## Collaborators

- Brueck, Hayat, Ha (UNM)
- Javey Group (Berkeley)
- Noh/Lee (KRISS)
- Cardimona (AFRL/VSSS)
- Gunapala Group (JPL)
- Painter Group (Caltech)
- QmagiQ LLC
- Raytheon Vision Systems
- Lin Group (RPI)
- Vandervelde (Tufts)
- SK Infrared LLC
- CINT

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- Maya Kutty
- Nutan Gautam
- Brianna Klein
- Ted Schuler Sandy
- Glauco Fiorante
- Vince Cowan
- Marziyeh Zamiri
- Ali Shirazi
- Nathan Henry (UG)

## Funding Agencies

AFOSR, AFRL, NSF, IC,  
DIA, DARPA, KRISS-GRI